

# Radioisotope Energy Sources

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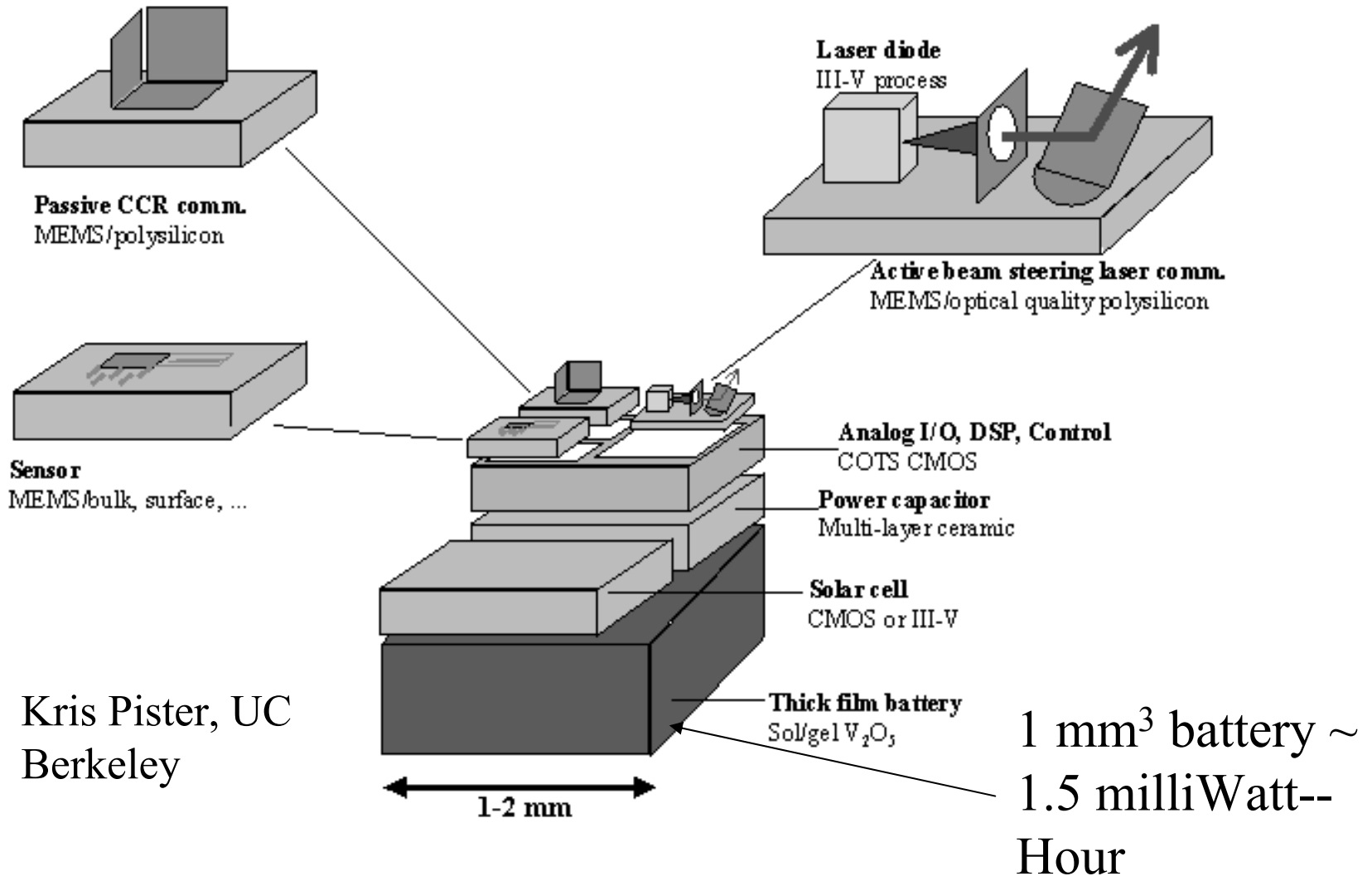
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# Outline

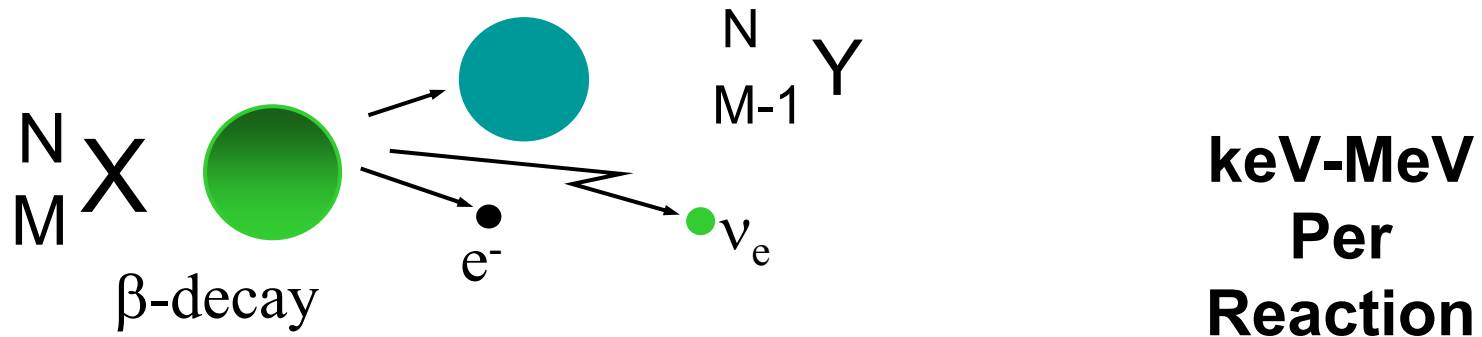
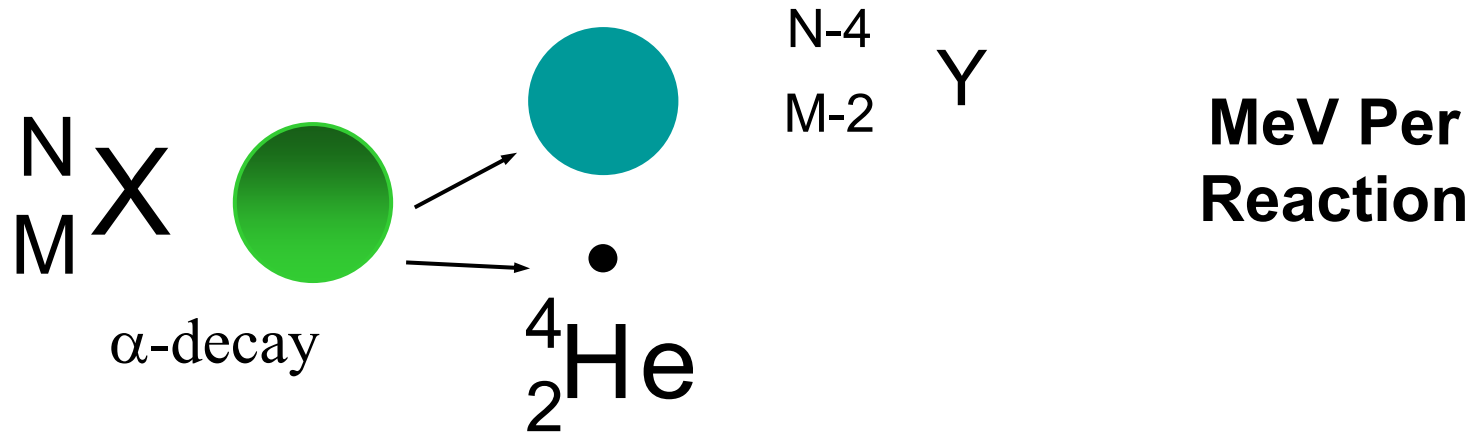
- Radioisotopes
  - Self-reciprocating cantilevers
- DC-biases for sensing and electronics
  - RF-pulses
  - Betavoltaics

# Autonomous Sensor Systems



Kris Pister, UC  
Berkeley

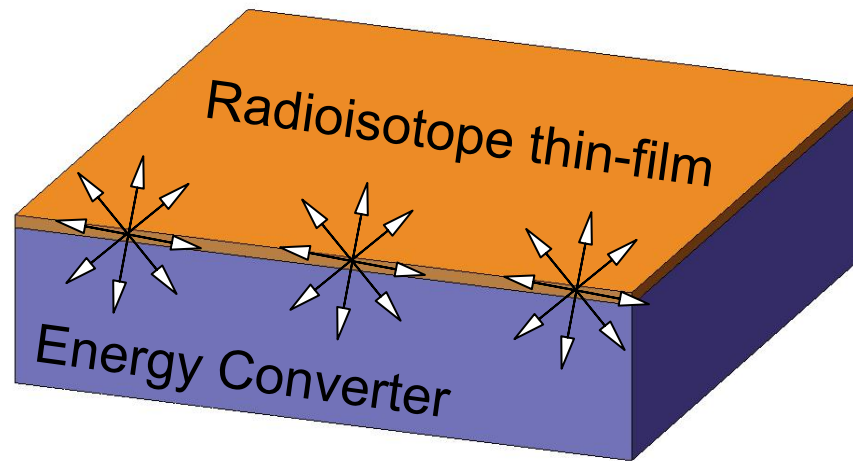
# What is the smallest power source?



- **Ultimately Scaled Power Source**
- **Conversion efficiency can in principle reach 100%**

# Radioisotope **Thin Film** Energy: Emission, *not Fission or Fusion*

Emitted particles



$$\bullet P_{\text{out,R}} = N_{\text{out,R}} \times E_{\text{avg}}$$

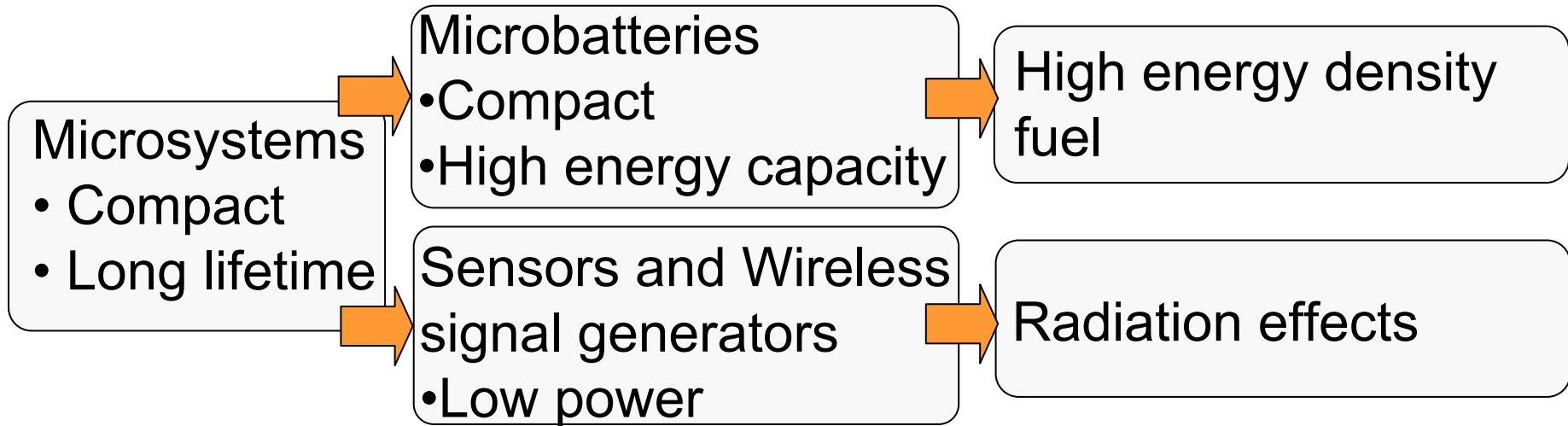
$$\bullet N_{\text{out,Pm-147}} : 830 \text{ Curie/g} \times 3.7 \times 10^{10} \text{ emissions/s/Curie}$$

$$\bullet E_{\text{avg,Pm-147}} : 63 \text{ keV}$$

$$\rightarrow P_{\text{out,PM-147}} : 0.309 \text{ W/g} \rightarrow \mathbf{2.05 \text{ W/cc}}$$

\*H. Flicker et al., "Construction of a Pm-147 Atomic Battery," IEEE Trans. Electron Devices, 1964.

# Why Radioisotope Thin-films?



Fuel	Energy Density
Electrochemical (Li-ion)	~10 kJ/cc
Hydrocarbon (Methanol)	~20 kJ/cc
Radioisotope ( $^{147}\text{Pm}$ , over 5.2 yrs)	170000 kJ/cc

**Reliability:** A radioisotope decays exponentially in time at a rate independent of ambient conditions like temperature, humidity

# Safety: Radioisotopes Around Us



Americium-241 in Domestic Smoke Alarms



Tritium in Exit Signs



30% of Pacemakers implanted from 1971-75 were radioisotope powered



## RADIOISOTOPE HEATER UNIT •

- HEAT OUTPUT — 1 WATT
- FUEL LOADING — 33.6 Ci
- WEIGHT — 1.4 OZ
- SIZE — 1 IN x 1.3 IN

- NASA's RHU
- 33 Ci
- 1 Watt output
- 1.4 oz.
- 1 cubic inch
- 2.7 g of Pu-238 (oxide form)
- Rugged, reliable



# Radioisotope Comparison

Low energy beta-  
easy to integrate

Isotope	Average energy (KeV)	Half life (year)	Specific Power (W/g)	Estimated Range in Si (Max.) (microns)
63-Ni	17	100.2	0.0067	21
3-H	5.7	12	0.33	2
147-Pm	67	~0.2	55	
210-Po	5300	0.38	140	26
238-Pu	5500	88	0.56	27
244-Cm	5810	18	2.8	28

Low energy beta- hard to integrate

Higher energy beta

Alpha sources:

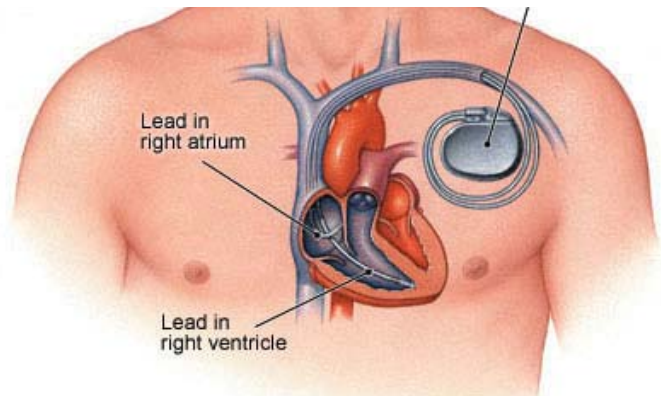
- Chemical toxicity
- Damage



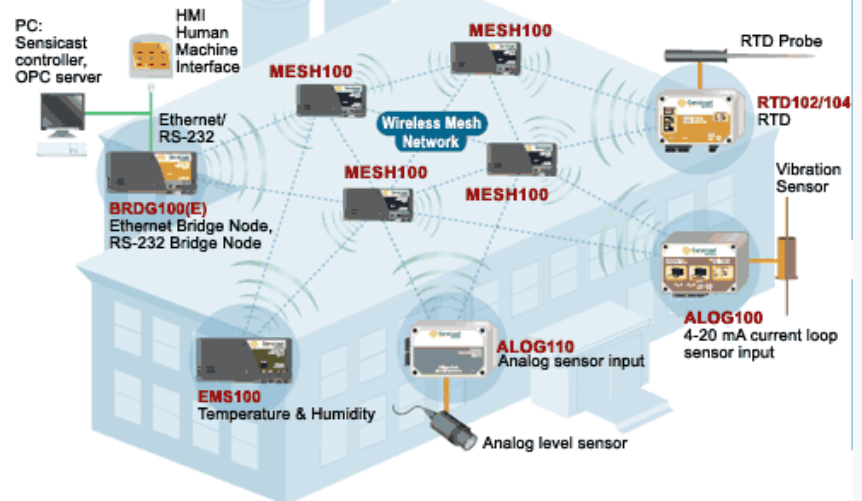
# Radioisotope Thin-film Powered Autonomous Microsystems

Enabling compact, long-lifetime, inexpensive, & safe

Implantable Medical Devices such as Pacemakers



Wireless Sensor Networks



100'  $\mu$ W continuously

10-100  $\mu$ W pulsed for sensing,  
1-100mW for communication

# Nickel-63 ( $^{63}\text{Ni}$ )

## Safety

- Penetration range of
  - primary radiation:  $<50\ \mu\text{m}$  in most solids
  - secondary radiation: None
- Effusivity: No effusion from thin-film sources even @ 400C
- Chemical toxicity: OSHA regulations permit work without any shielding, 2 millicurie annual intake limit\*

## Power generation characteristics

- Half-lifetime: 100.3 years
- Specific activity:  $\sim 10$  curie/g
- $E_{\text{rad,avg}}$ : 17.3 keV  $\rightarrow$   $P_{\text{out,dens}}$ : 0.1-1  $\mu\text{W}/\text{cm}^2$

Human Health Fact Sheet, Argonne National Laboratory, August 2005

Williams, D. F., "Recovery and purification of nickel-63 from hfir-irradiated targets," Oak Ridge National Laboratories, Tech. Rep., 1993

# Classical Categories of Radioisotope Power Sources

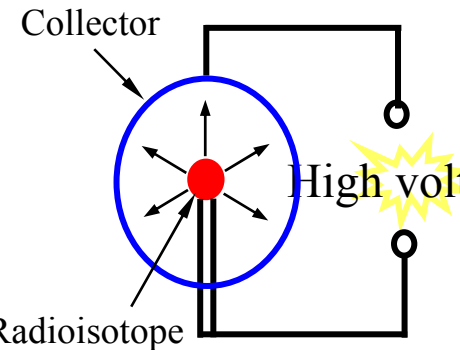
## Kinetic energy

## Charge



### Vacuum

- Direct charge collection and storage



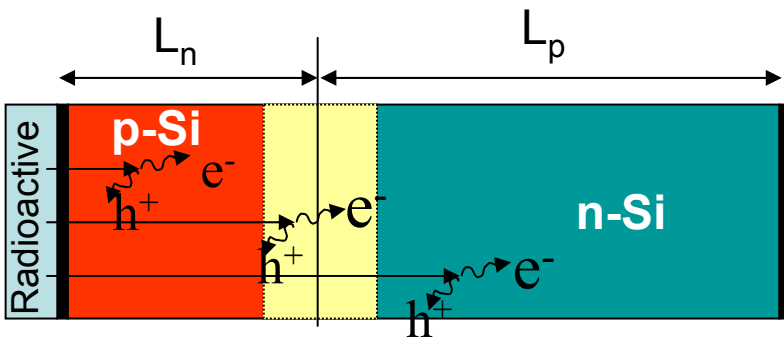
### Ionization

- Liquids – photon creation – liquid scintillation
- Gases – ion-electron generation

Semiconductors: e-h+ creation – damage to lattice

### Thermionic, Thermoelectric

- Thermal to electric conversion

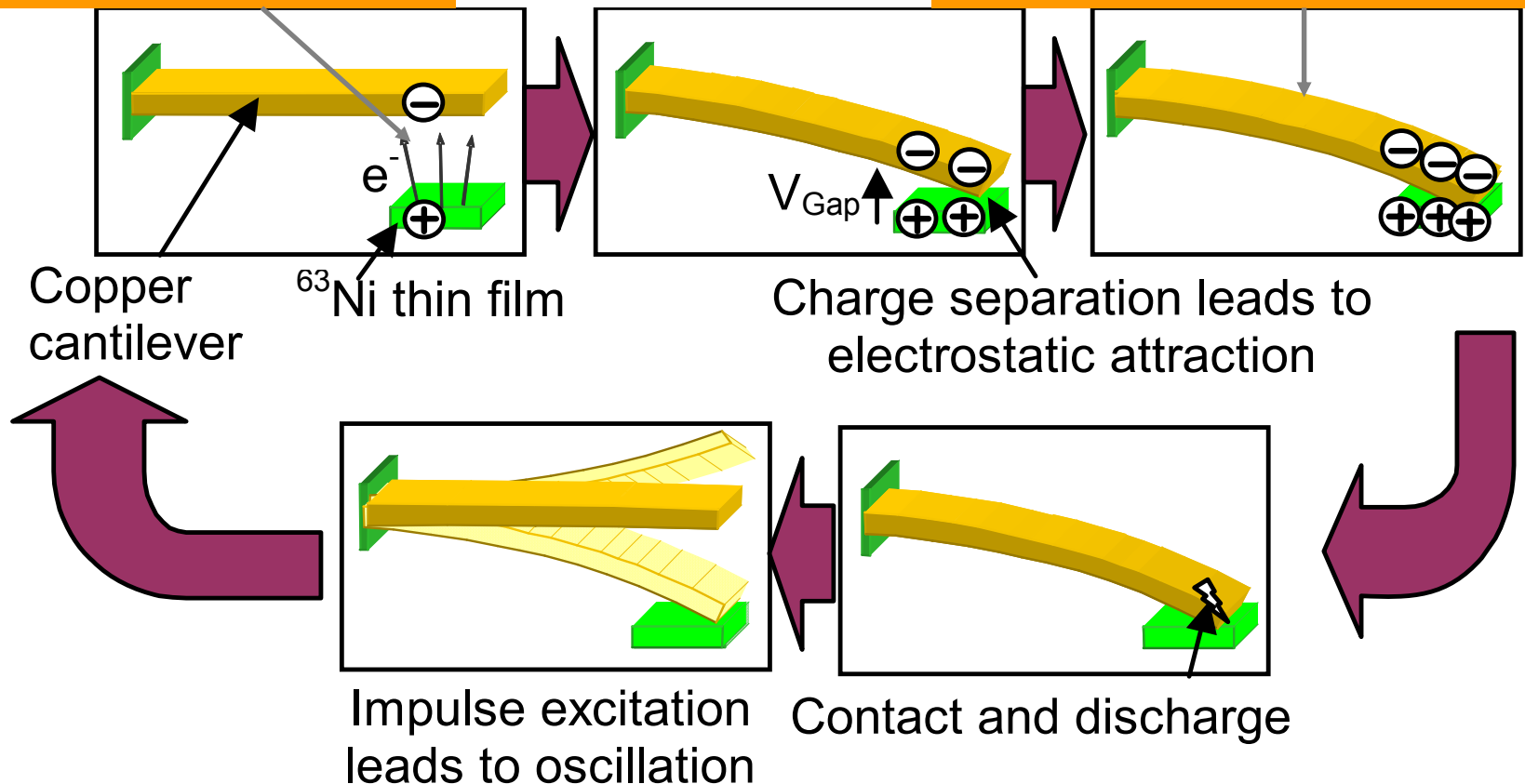


### Betavoltaic

# Self-Reciprocating Cantilever

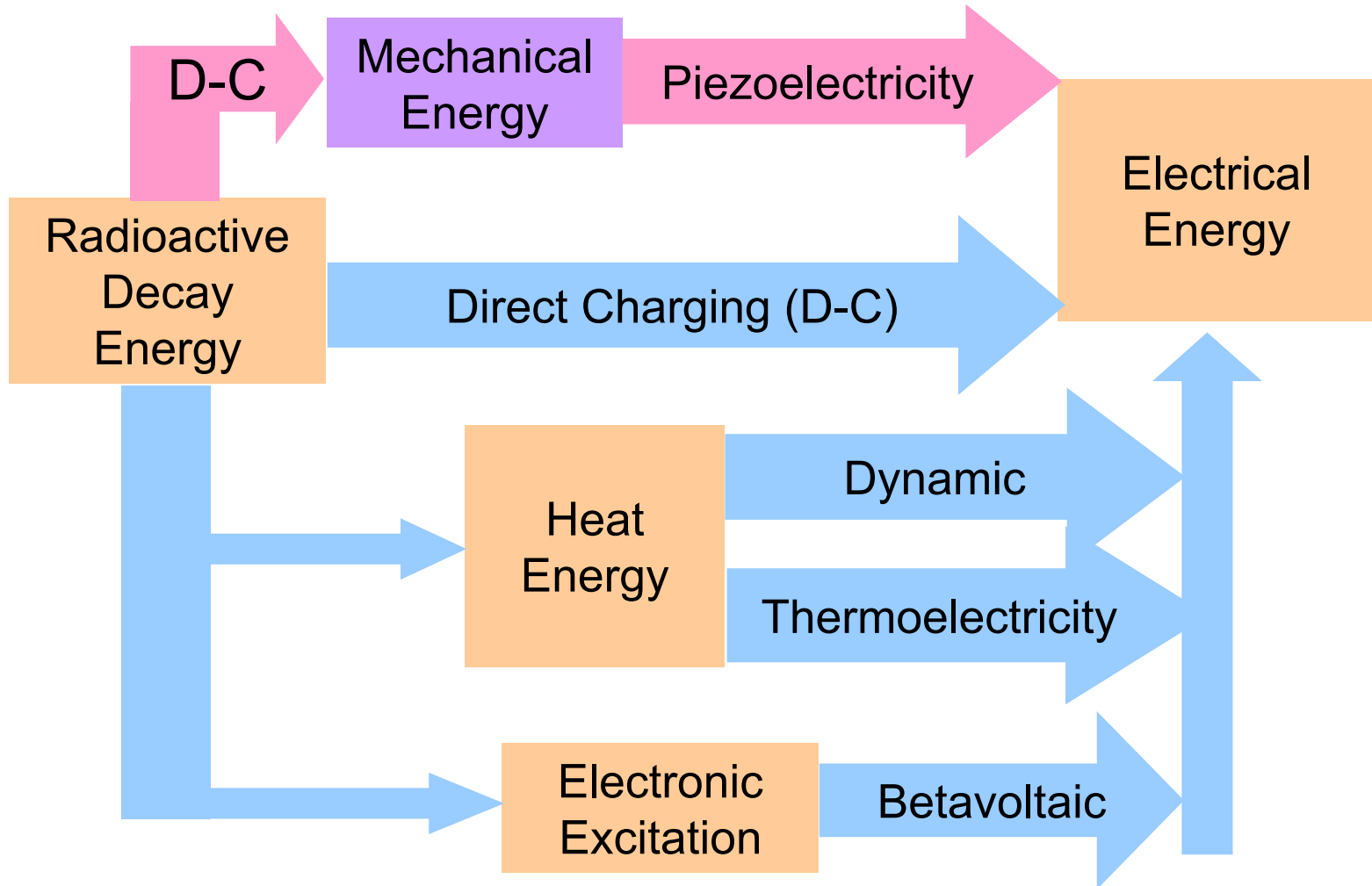
Kinetic energy in the  $\beta$ -particles emitted

Mechanical energy stored in the deformed cantilever

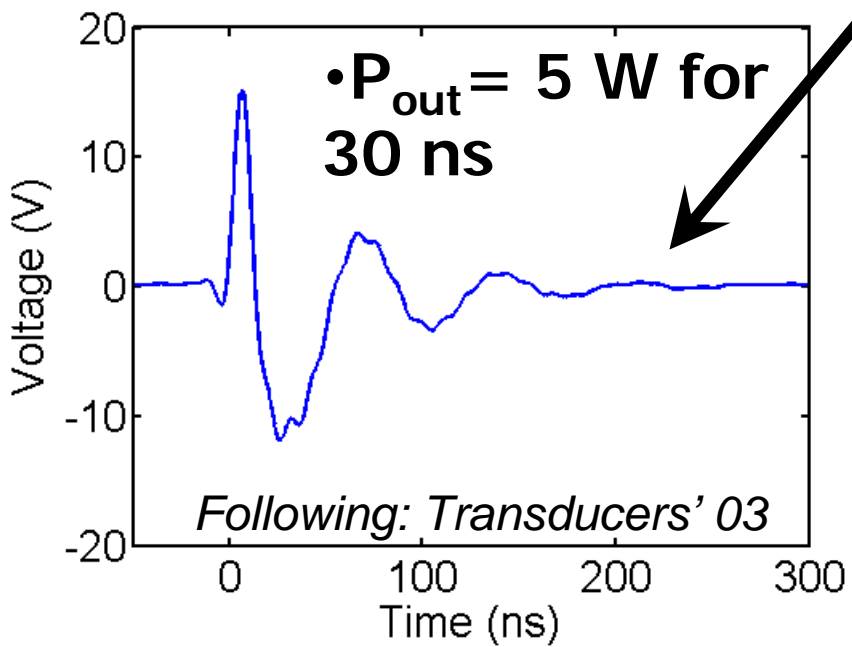
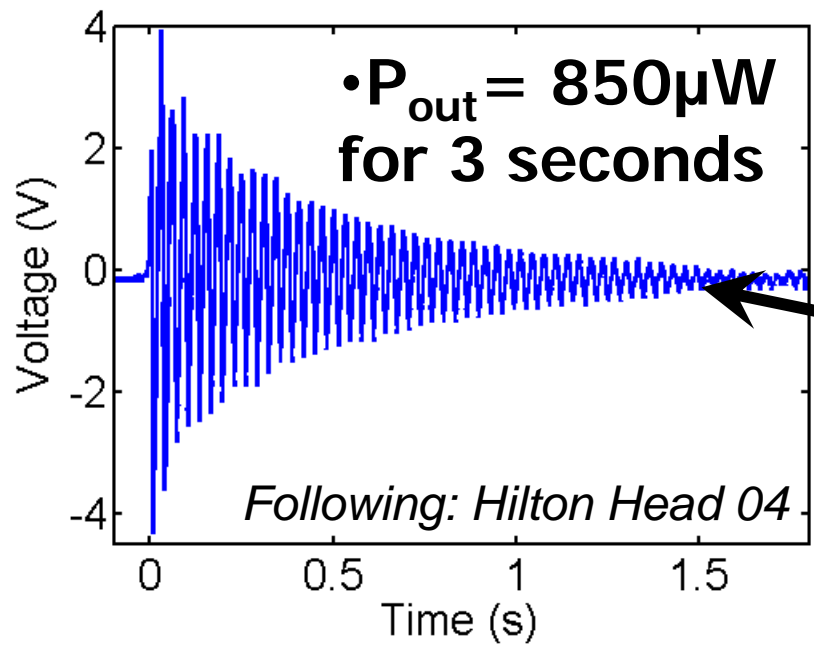


H. Li, A. Lal, J. Blanchard, D. Henderson, Journal of Applied Physics, 2002

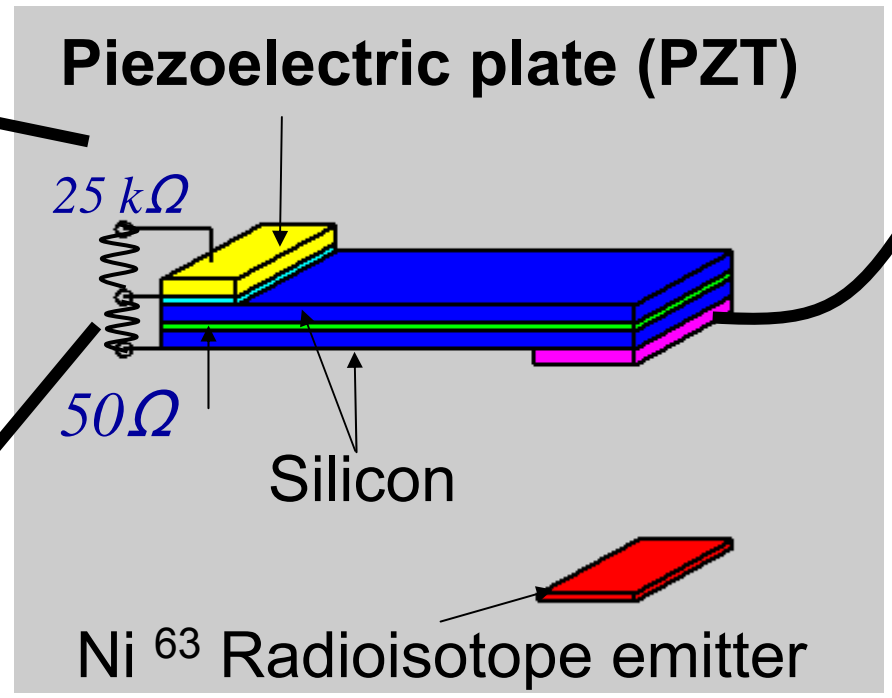
# Radioisotope-powered Electro-Mechanical Power Generator (REMPG)



# The Handbuilt Device

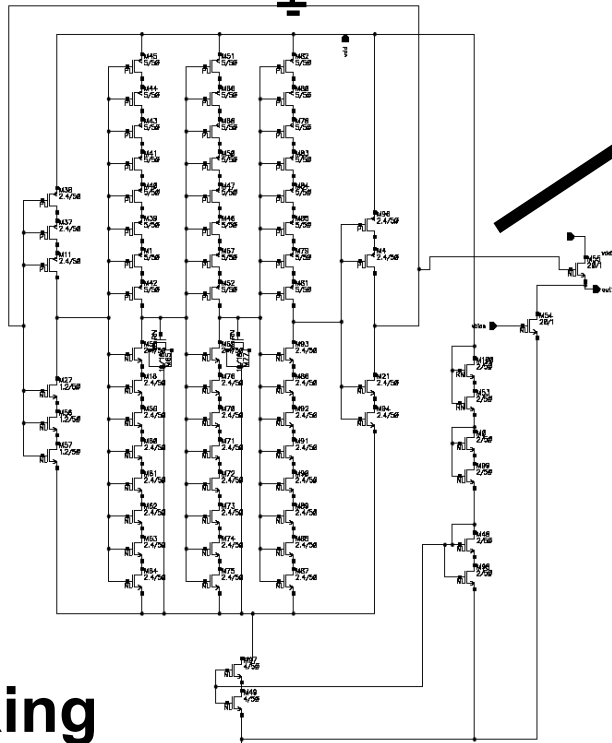
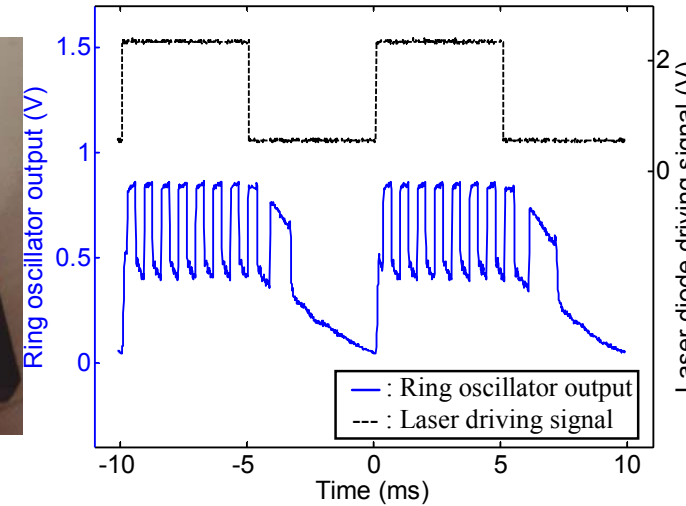
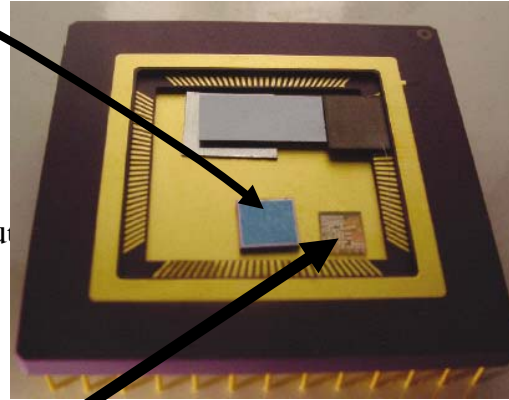
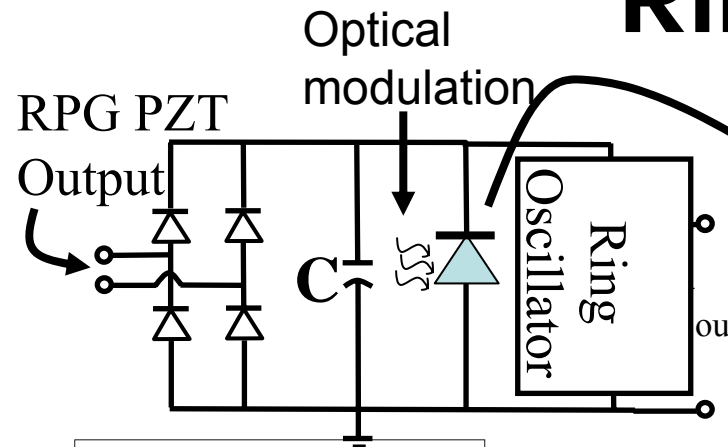


- Betavoltaic collector  
– 70 nW continuous



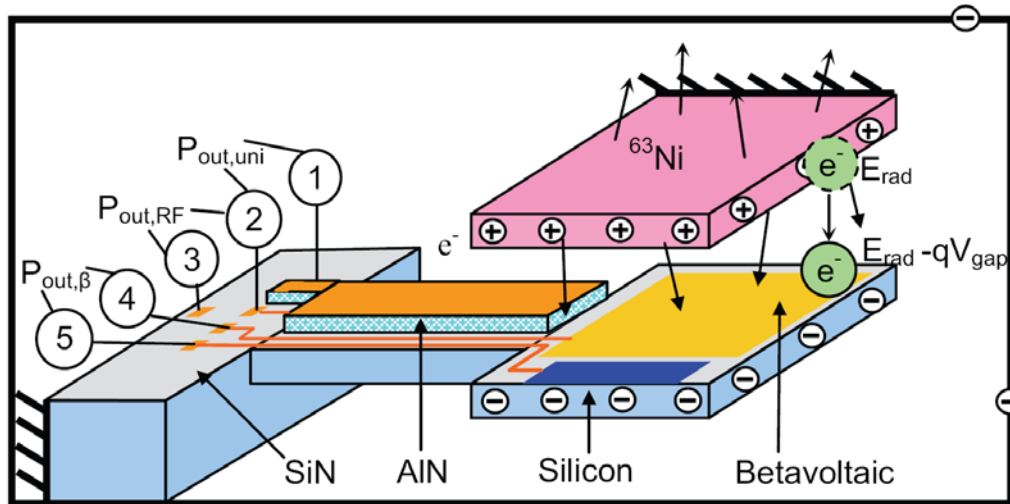
- Power output for 10 mCi source
- Three power types produced from same device

# RPG Powered Photodiode/ Ring Oscillator



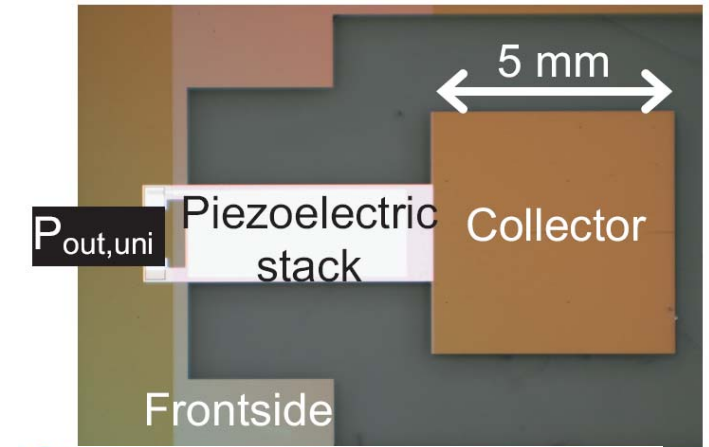
- A photodiode and a rectifier and ring-oscillator are powered by RPG
- Ring oscillator frequency is controlled by signal from photodiode

# IRPG (Integrated Radioactive Power Generator)



Vacuum chamber

1. PZT top electrode
2. PZT bottom electrode
3. Silicon cantilever
4. Betavoltaic p<sup>+</sup>
5. Betavoltaic n<sup>+</sup>

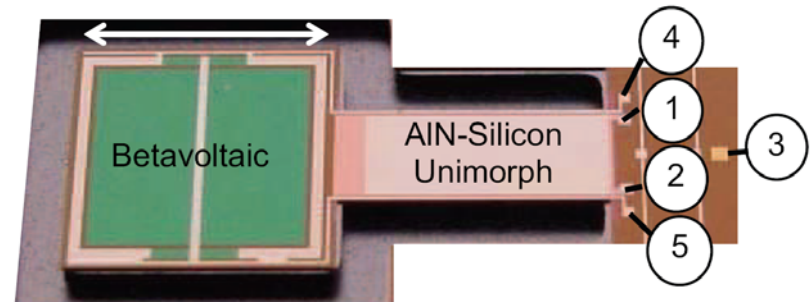
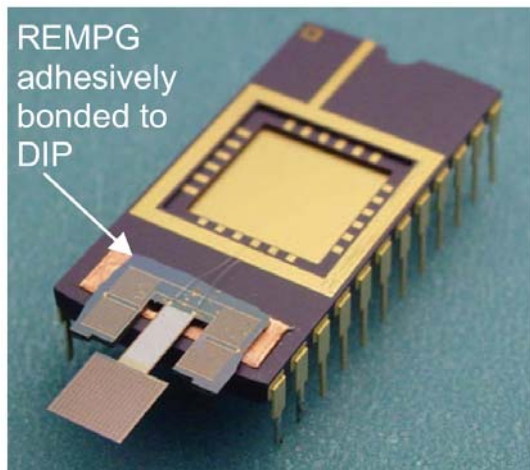


$$l_{cant} = 10\text{mm}, l_{piezo} = 4.5\text{mm}$$

$$w_{cant} = w_{piezo} = 2\text{mm}, t_{cant} =$$

$$42.5\mu\text{m}, t_{piezo} = 1\mu\text{m}$$

5mm

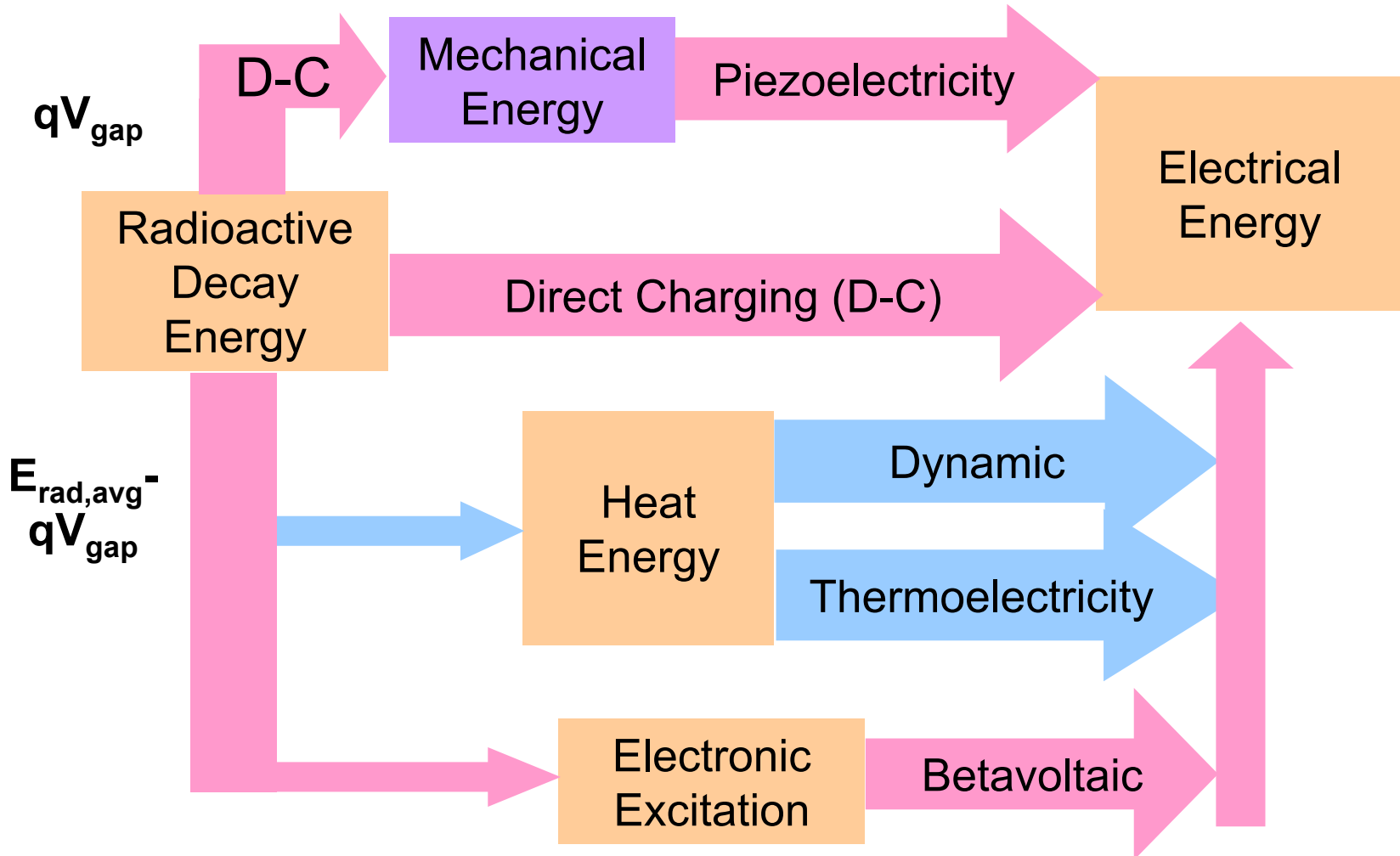


1. PZT top electrode
3. Silicon cantilever
5. Betavoltaic n<sup>+</sup>

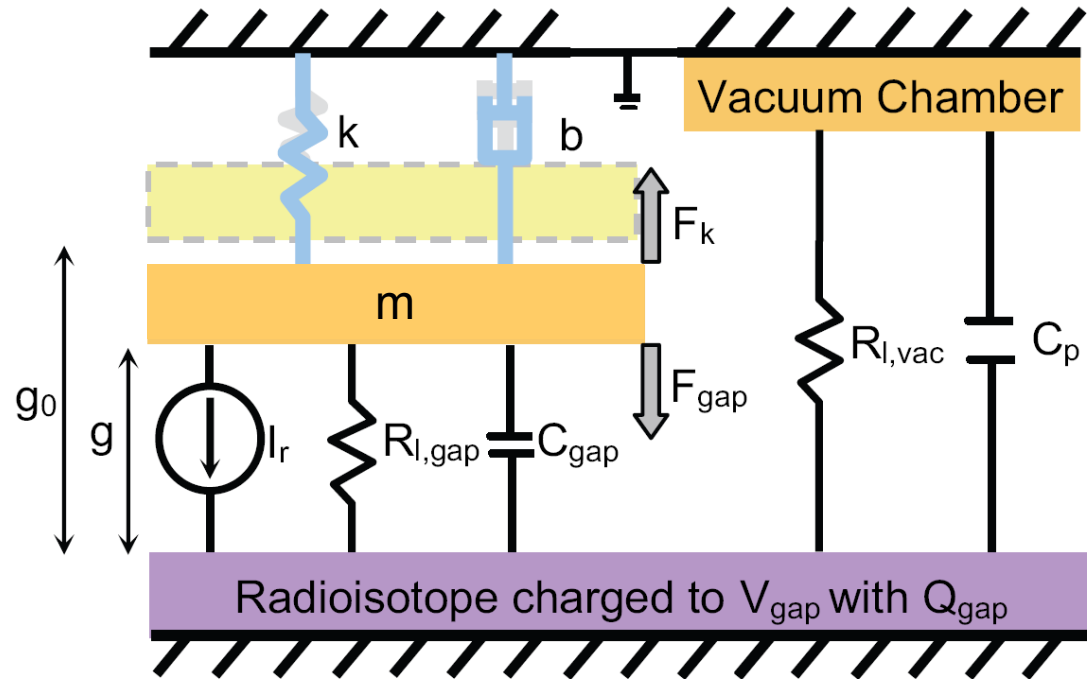
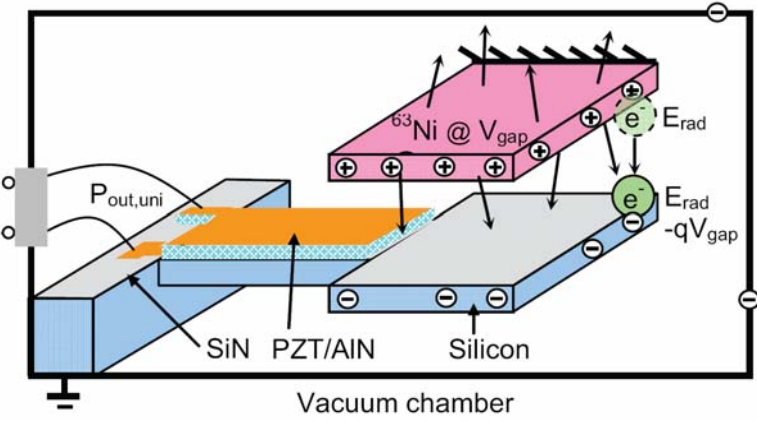
2. PZT bottom electrode
4. Betavoltaic p<sup>+</sup>



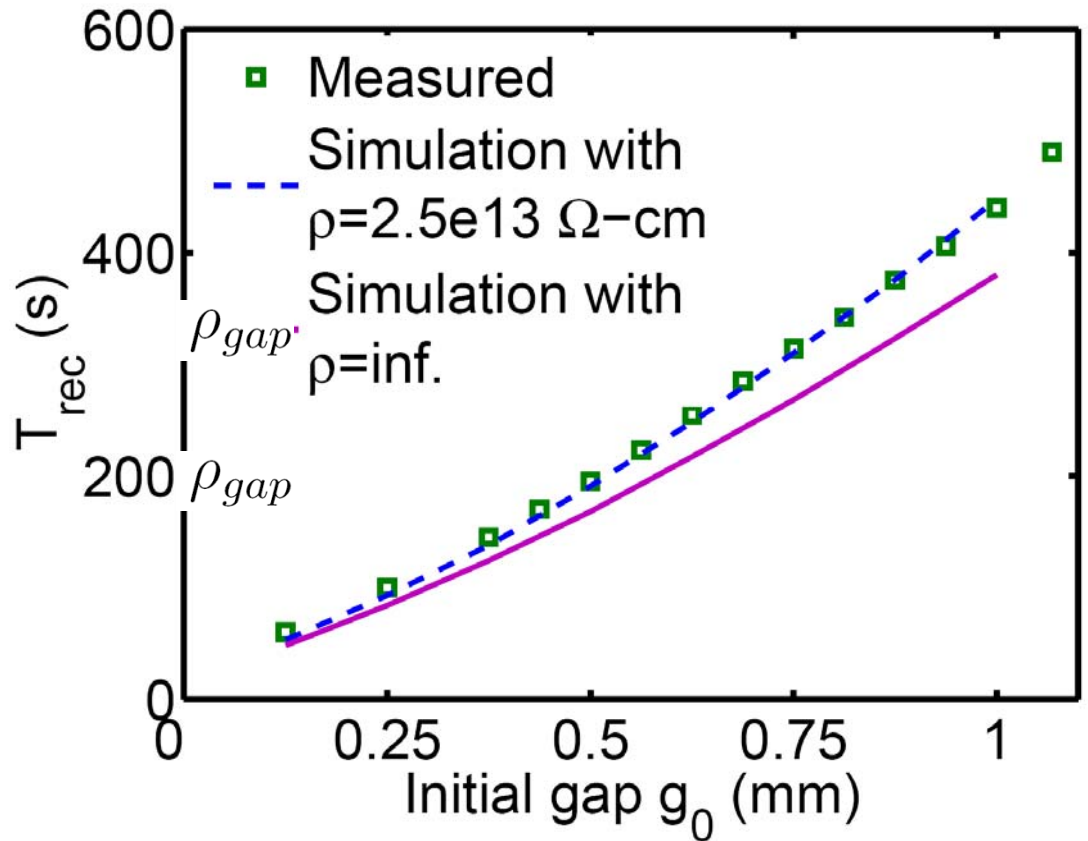
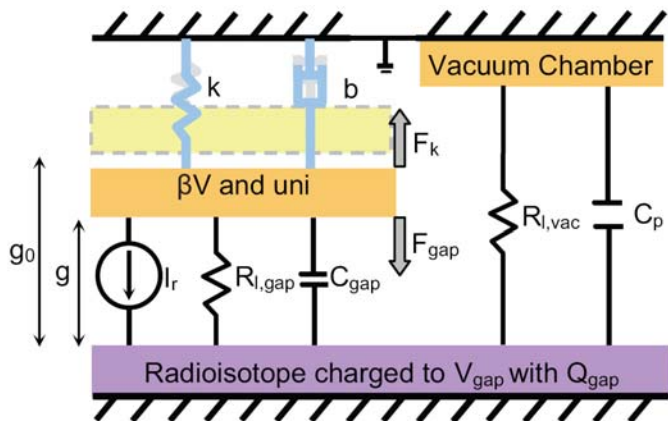
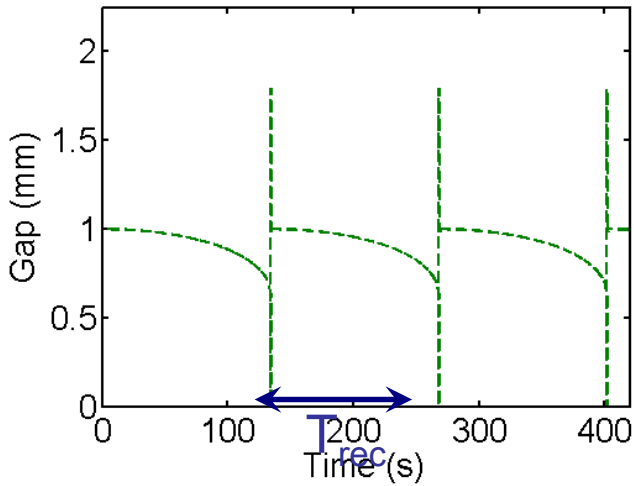
# Integrated Radioisotope-powered Electro-Mechanical Power Generator (IRPG)



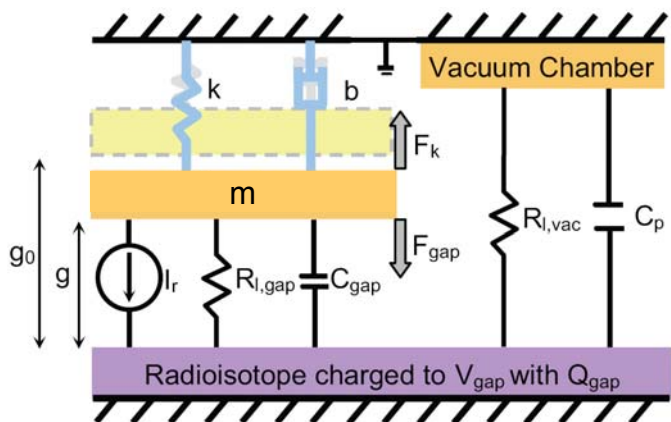
# REMPG Modeling



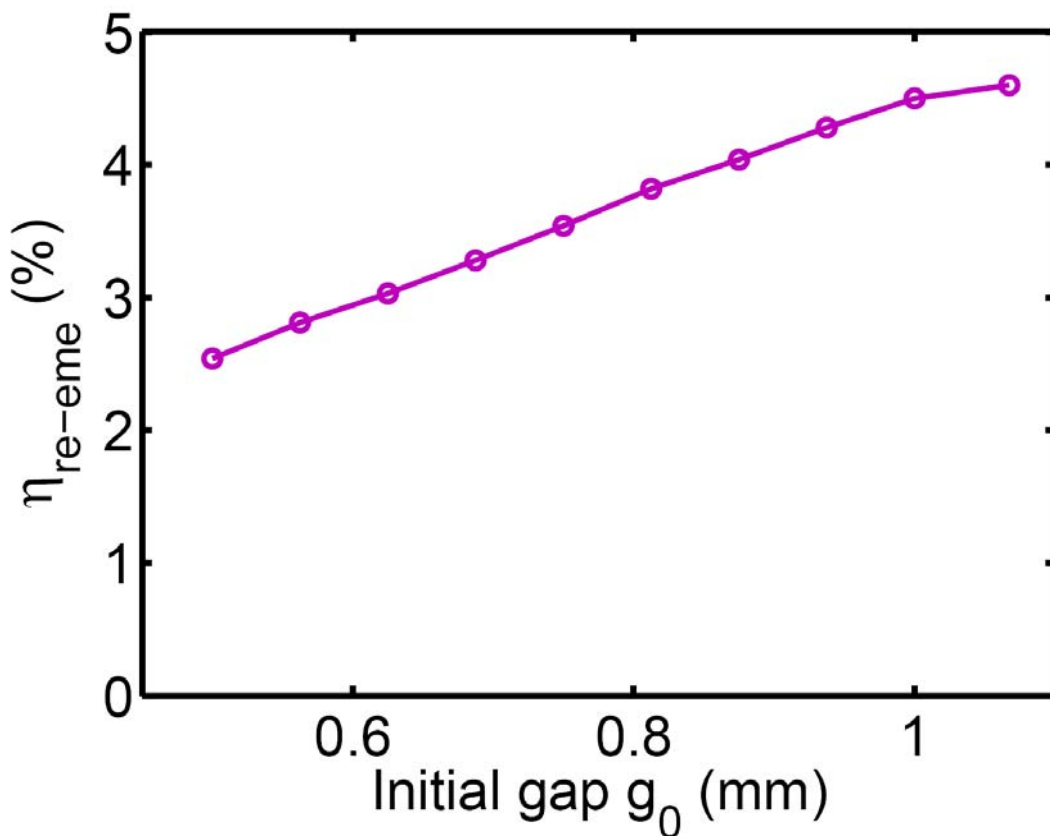
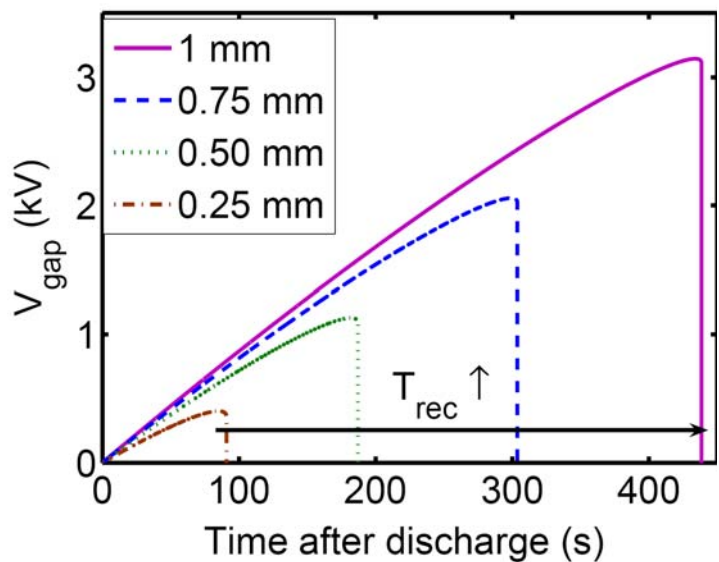
# Measured REMPG Reciprocation Period ( $T_{rec}$ )



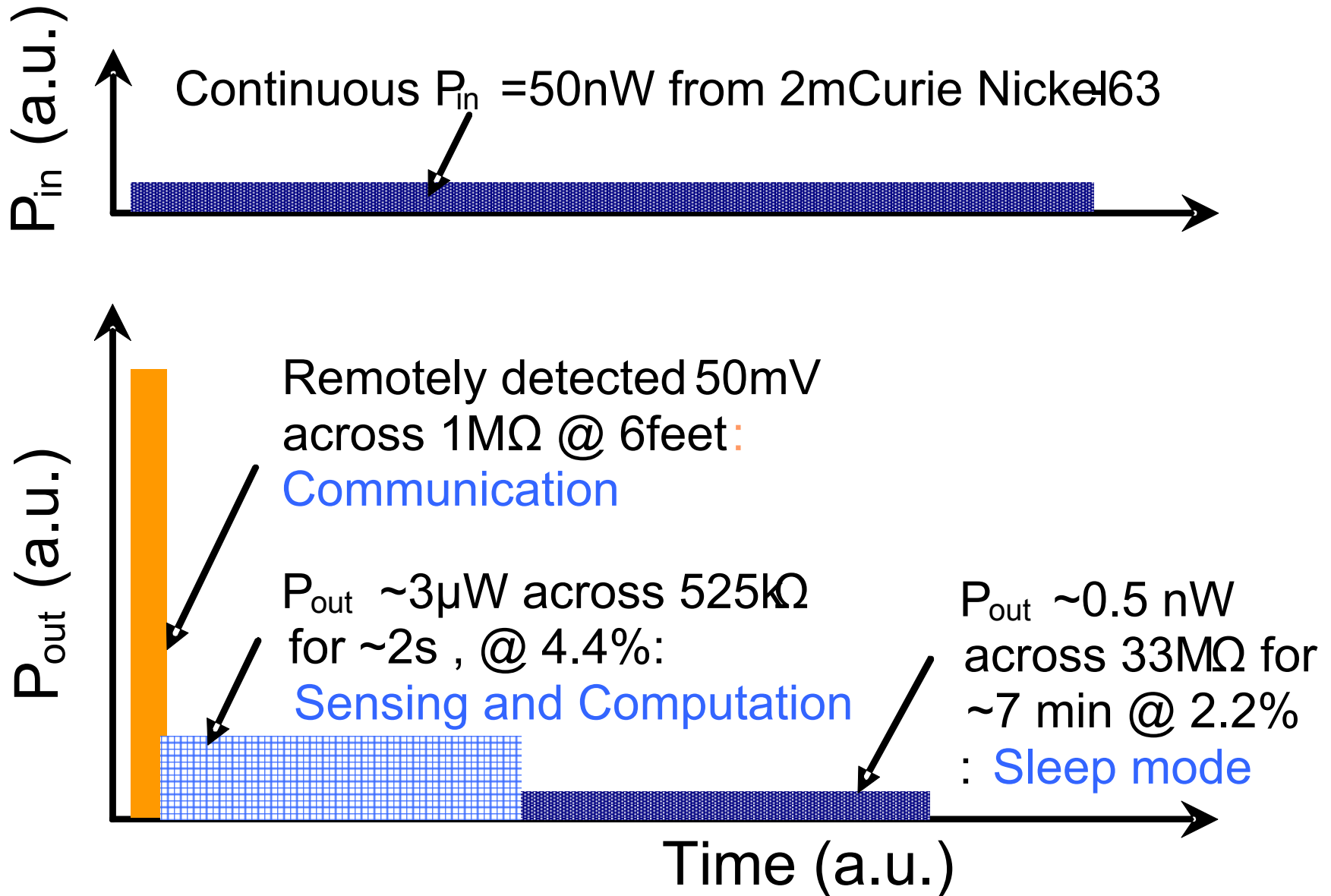
# Measured Radioisotope-Electromechanical Energy Conversion Efficiency



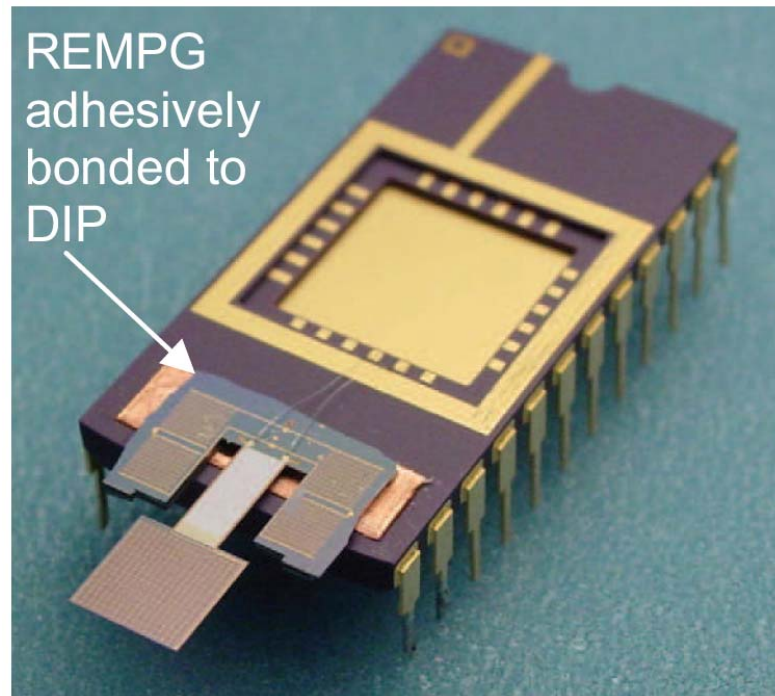
$$\eta_{re-eme} = \frac{E_{eme,rempg}|_{t=T_{rec}-\delta t}}{E_{in,rempg}}$$



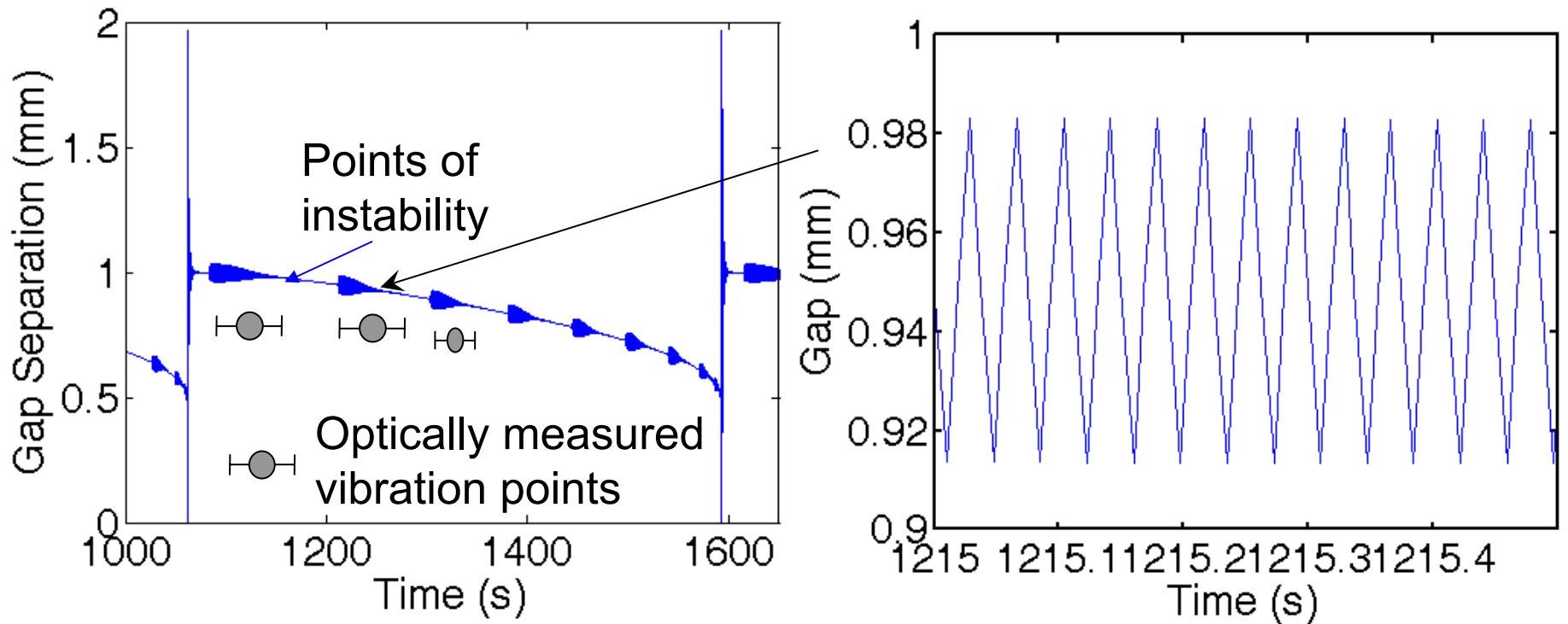
# IRPG Power Supply Model



# What About Vibration Scavenging From RPG?

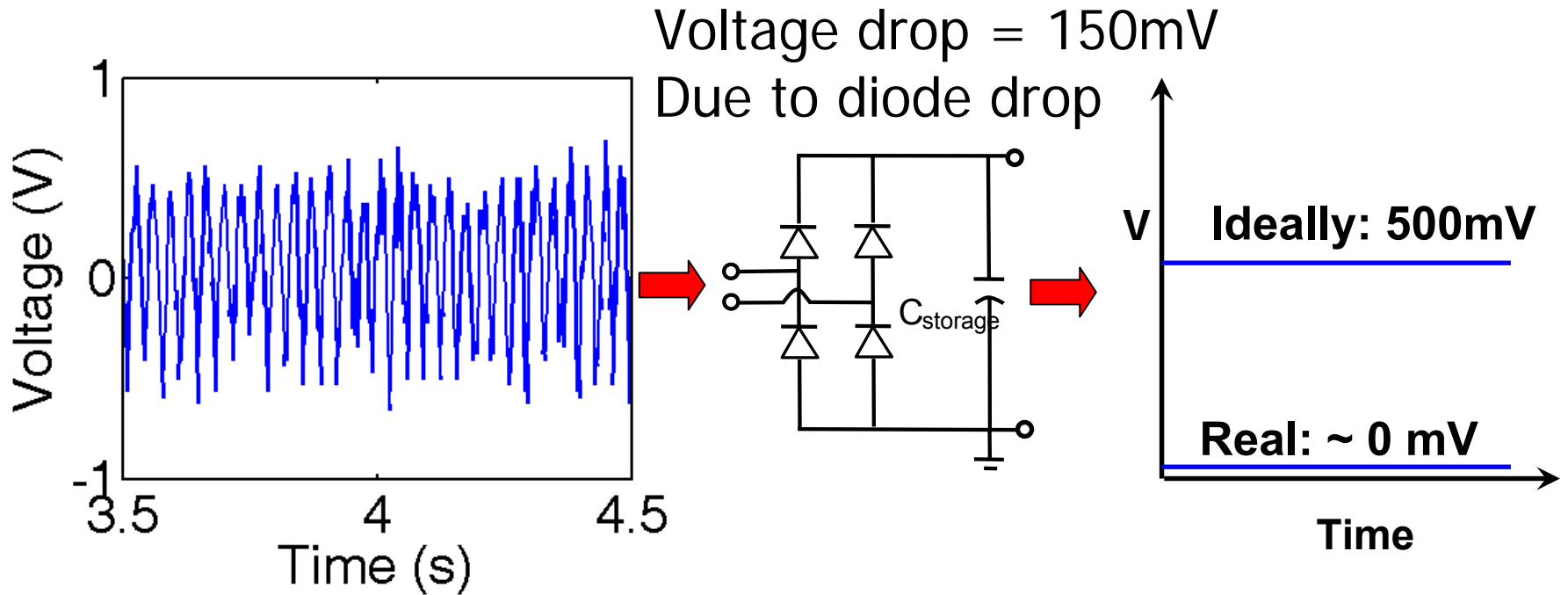


# Simulation and verification of continuous vibration modes



• **Simulink simulation and experimental observation proving continuous reciprocation in the RPG for high efficiency (23%)**

# The Bridge-Rectifier Problem

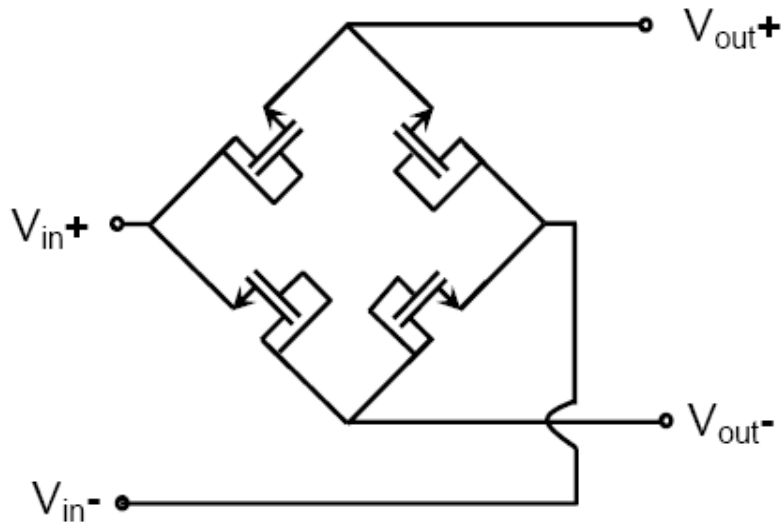


- 70 nW continuous output, at a conversion efficiency of **23%**, **but output voltages can be low**

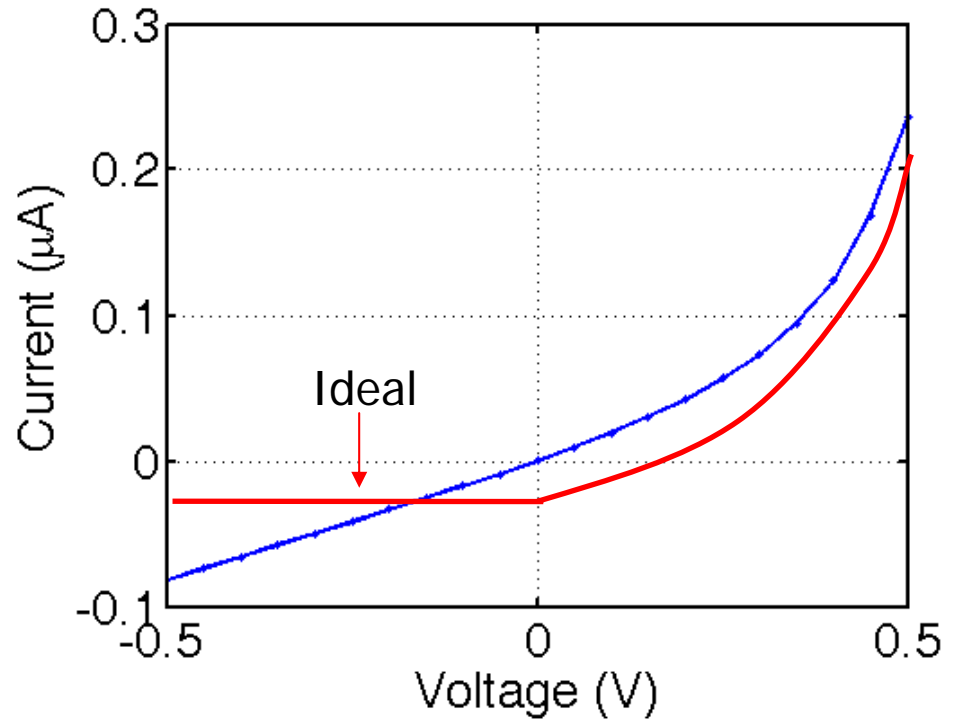
- Loss of voltage headroom kills efficiency
- Need low-voltage drop rectifier to improve efficiency



# Zero-threshold voltage MOSFET Bridge Rectifier ?

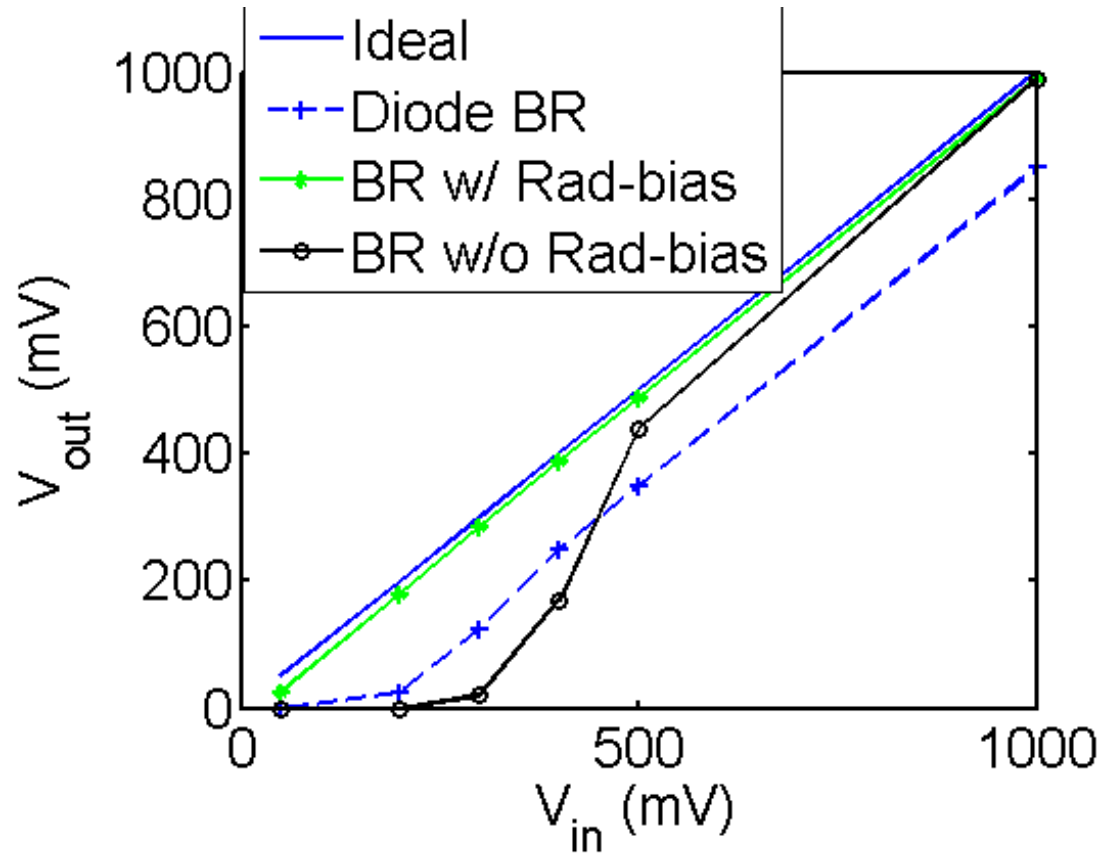
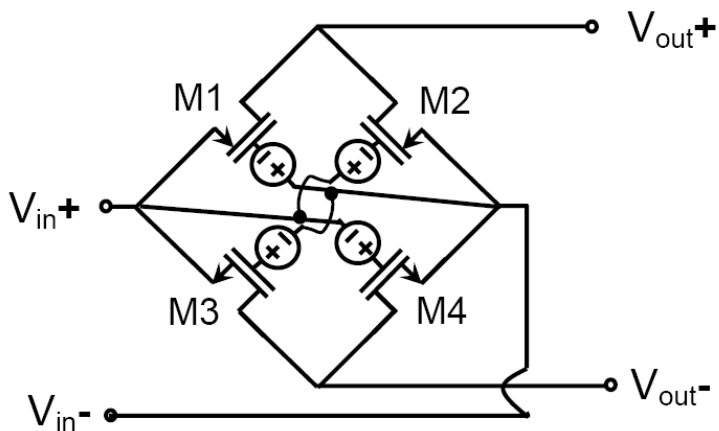
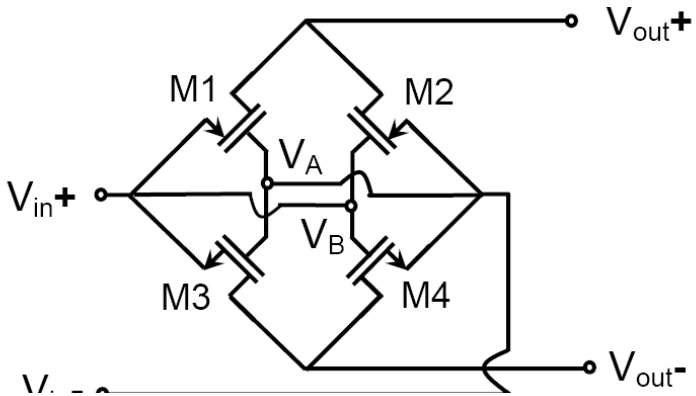
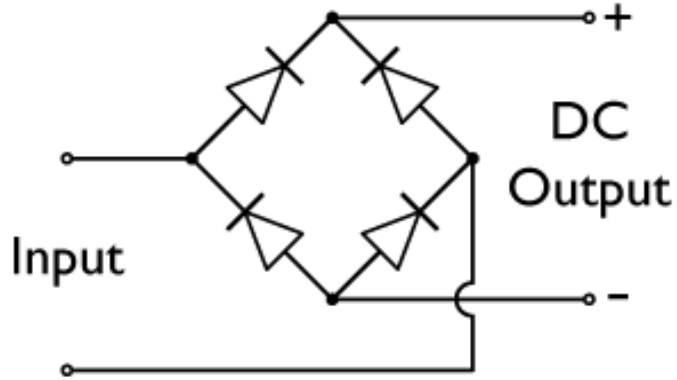


- Voltage drop = 450mV (measured in SoS 0.5  $\mu\text{m}$ ) for  $V_{th} = 0.455\text{ V}$
- Zero threshold MOS could minimize voltage dropout



- I-V characteristics of a diode connected zero threshold voltage n-MOSFET fabricated in the 0.5  $\mu\text{m}$  SoS technology

# Bridge Rectifier Comparison



- Radioisotope powered bias enables super-efficient bridge rectifier

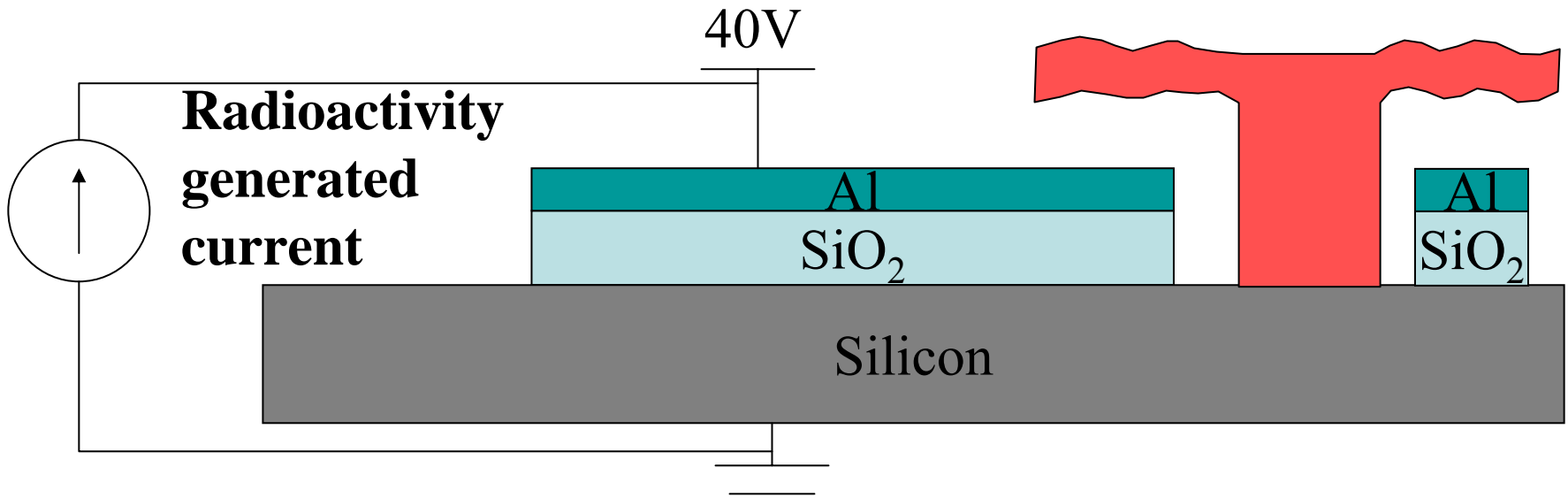
# Self-powered DC bias generation

$$I_{FN} = A_G A \varepsilon_{ox}^2 \exp\left(\frac{-B}{\varepsilon_{ox}}\right)$$

$$A = \frac{q^3 (m/m_{ox})}{8\pi h \Phi_B} = 1.54 * 10^{-6} \frac{(m/m_{ox})}{\Phi_B} \left[ \frac{A}{V^2} \right]$$

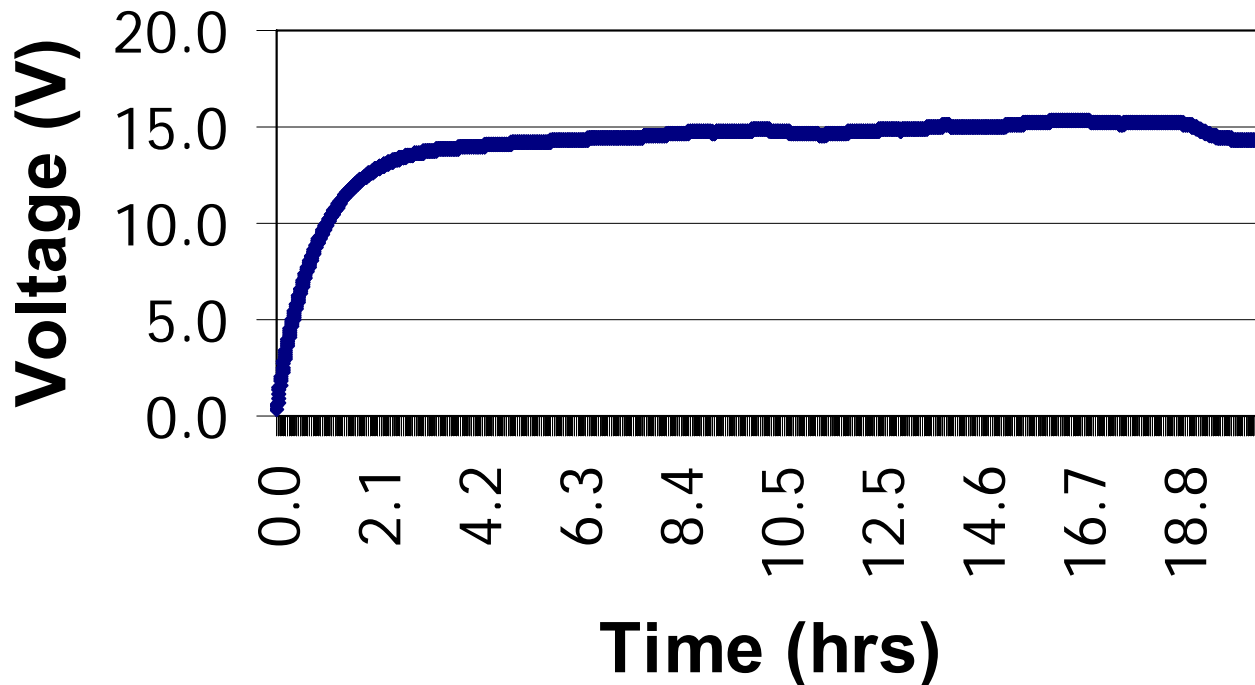
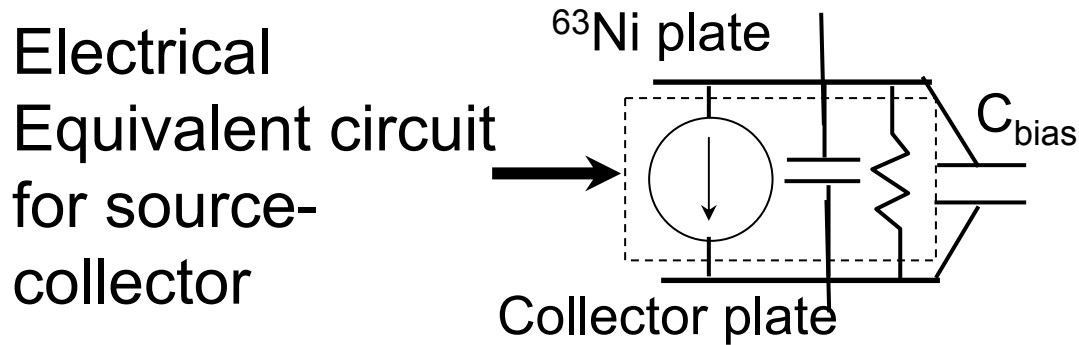
$$B = \frac{8\pi \sqrt{2m_{ox} \Phi_B^3}}{3qh} = 6.83 * 10^7 \sqrt{(m_{ox}/m) \Phi_B^3} \left[ \frac{V}{cm} \right]$$

- Where  $m_{ox}$  = Effective Electron Mass
- $m$  = Free Electron Mass
- $\Phi_B$  = Barrier Height at the Interface
- $A_G$  = Gate Area



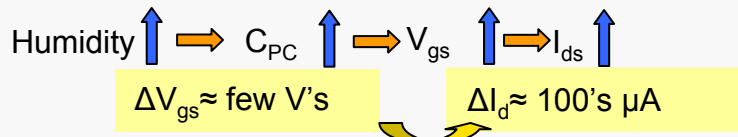
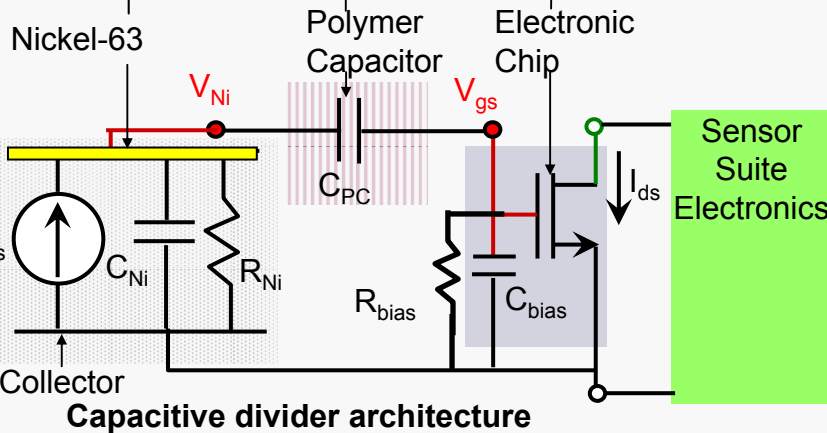
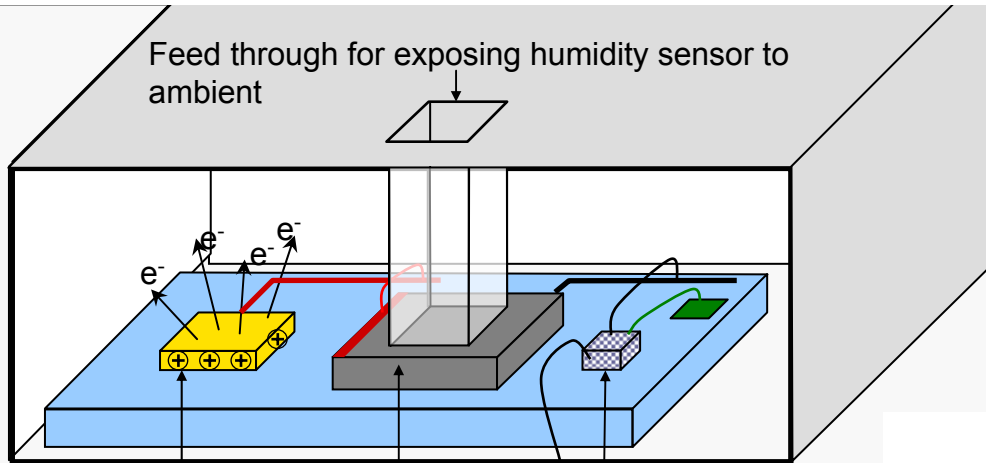
**Example: 10 nm oxide with 5 pA can generate 40V**

# Radioisotope-enabled 15 V source



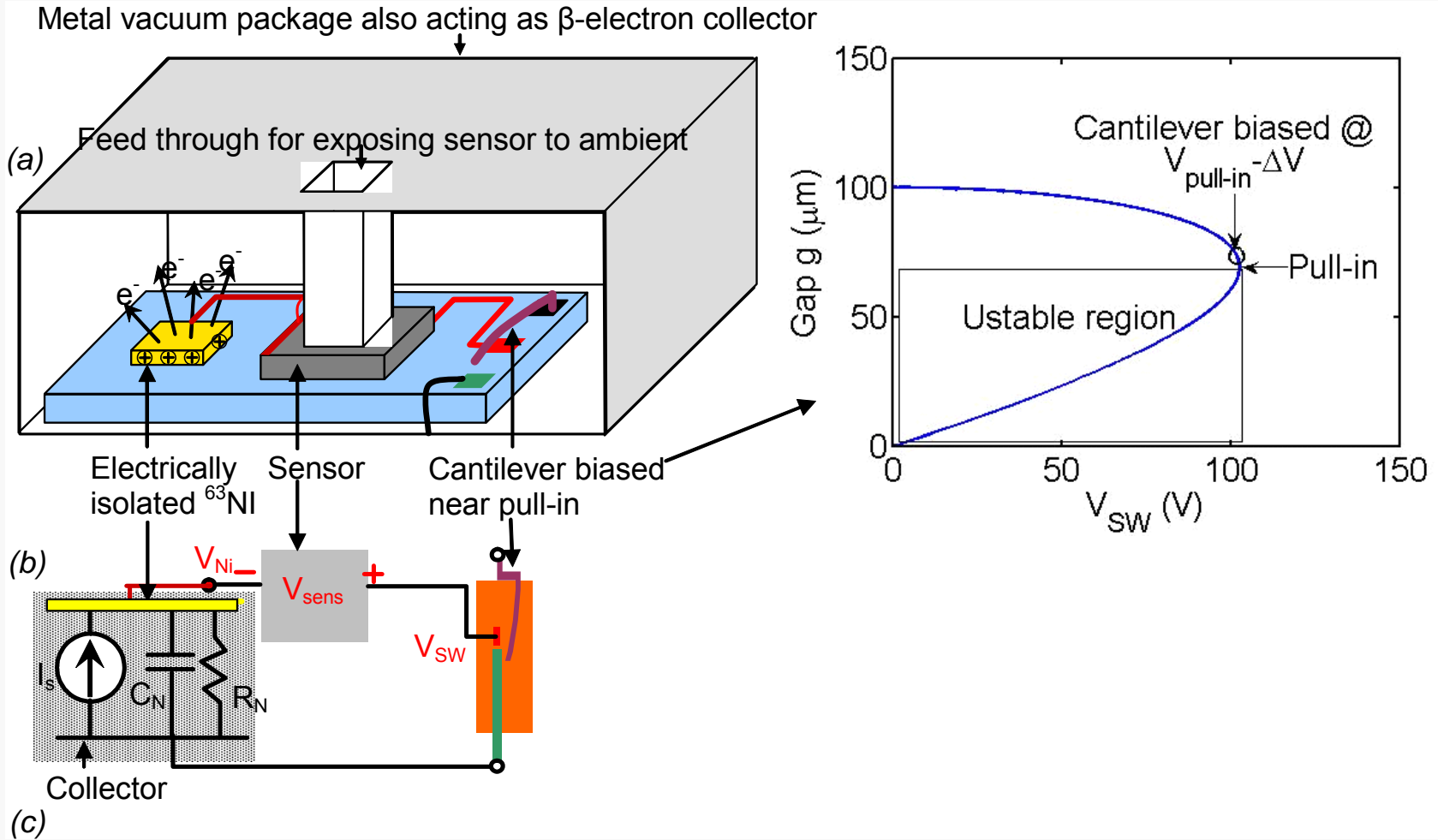
- 10 pF capacitor in parallel, 2 milliCi  $^{63}\text{Ni}$  source

# Self-powered Humidity Sensor: Concept

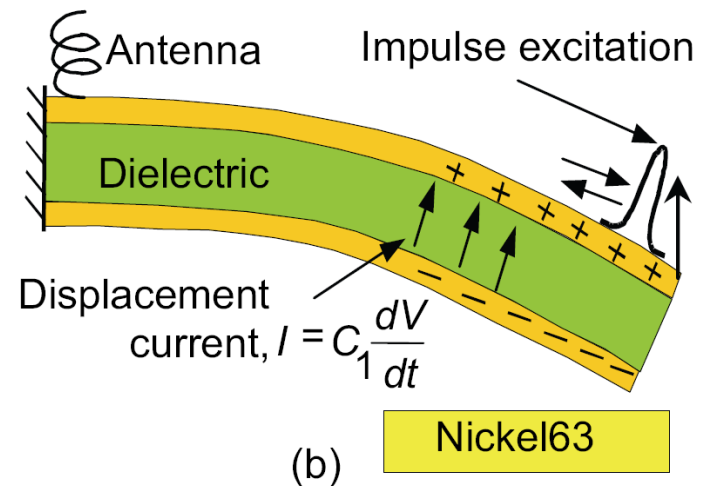
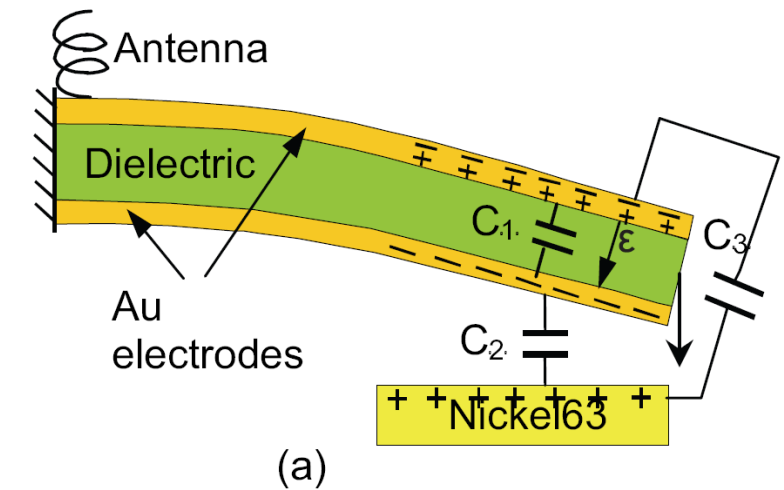
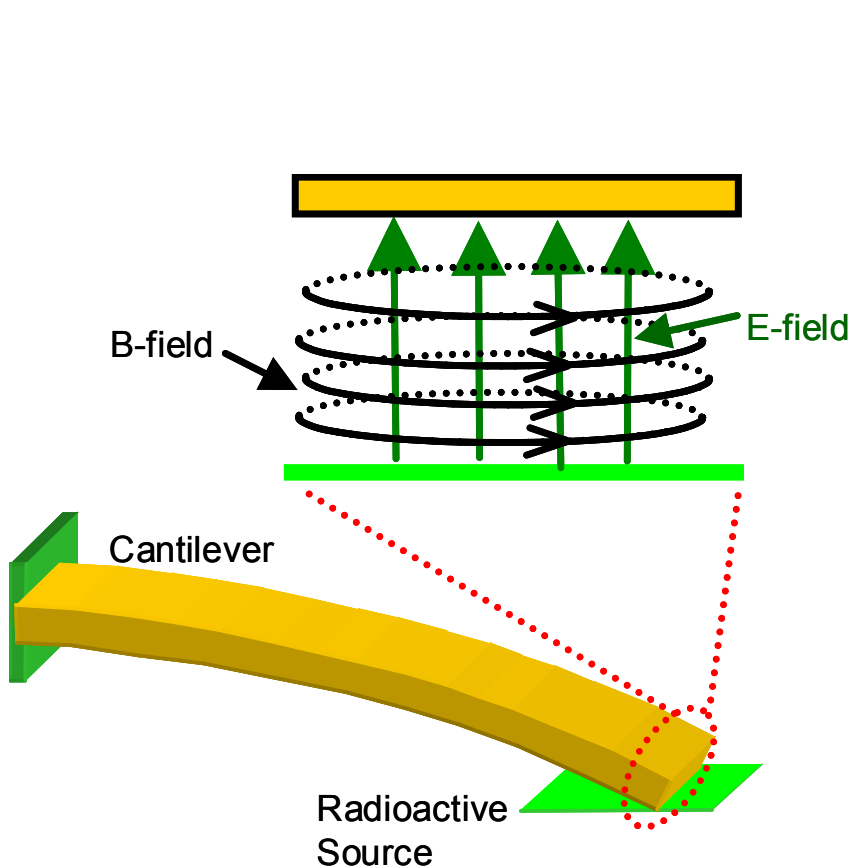


MOSFET Amplification

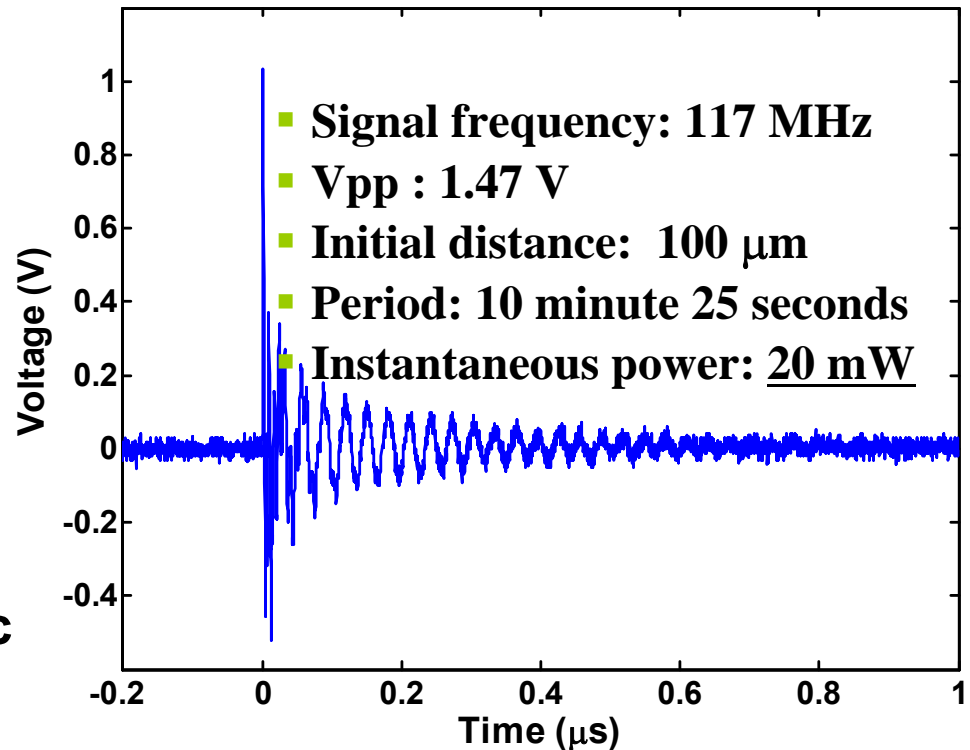
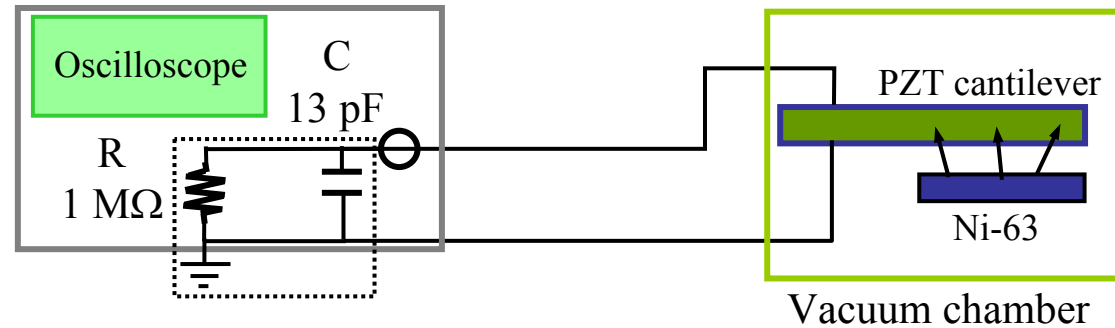
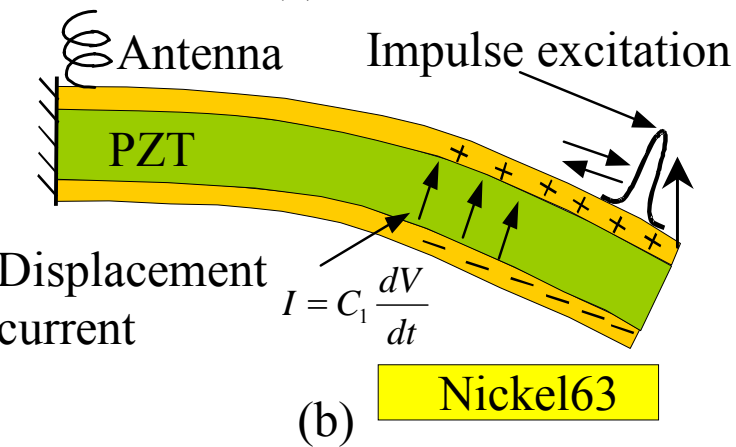
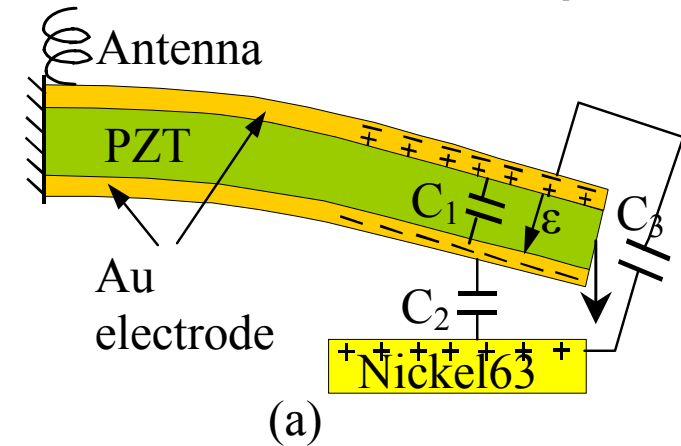
# Self-powered Sensor Vision



# Are we Utilizing All Energy in IRPG?



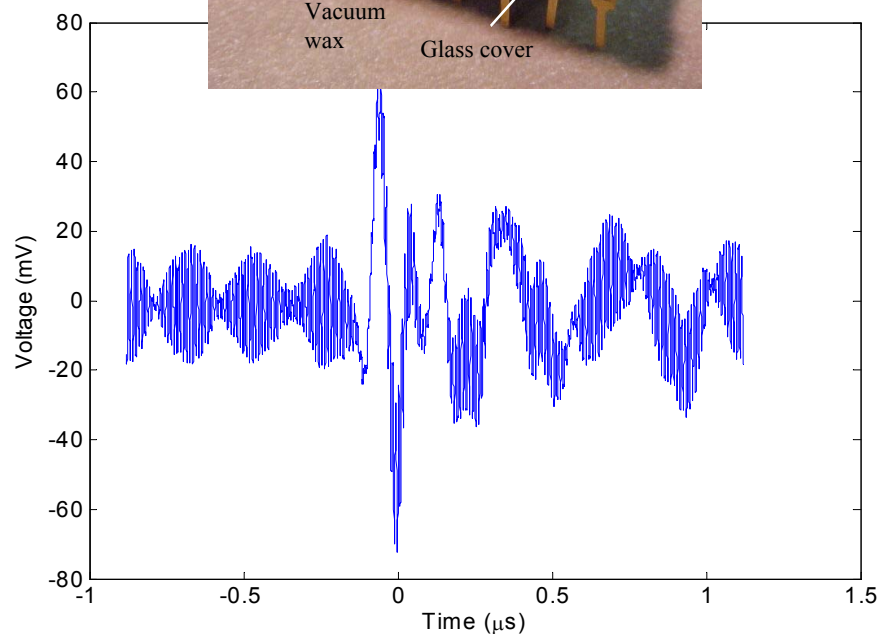
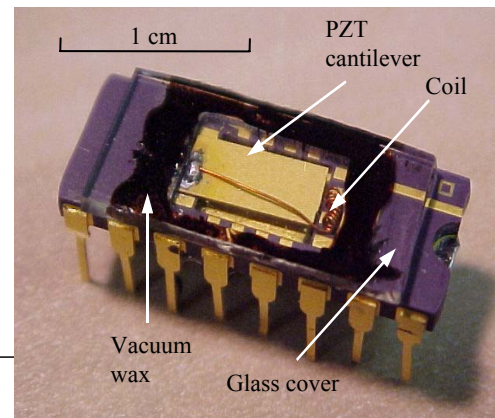
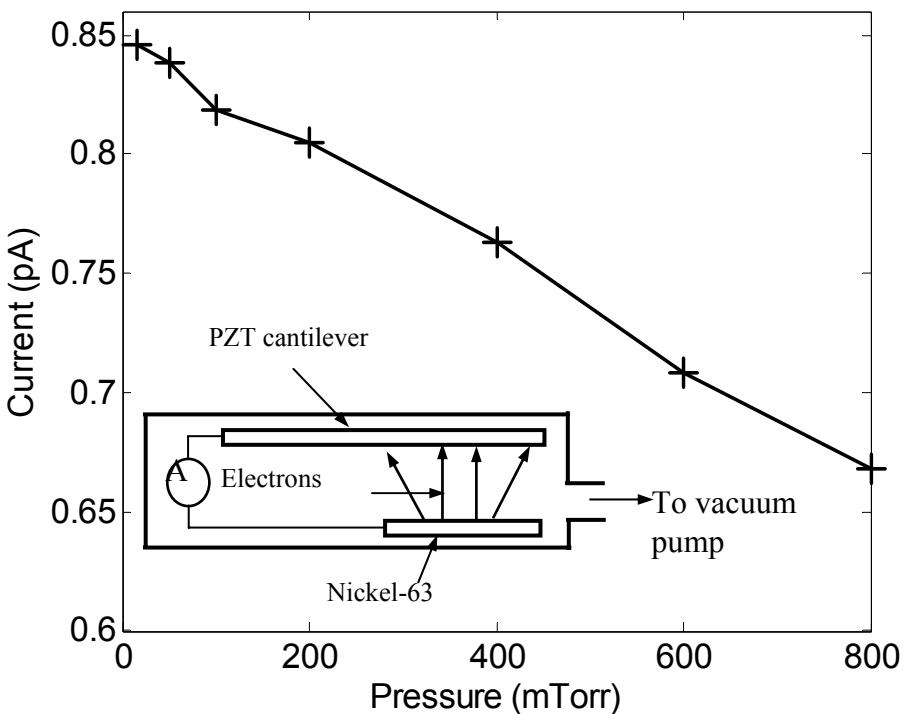
# Self-powered RF pulse generation



- Parasitic energy in dielectric
- Impulse response of dielectric is excited



# Self-powered Pressure Sensor



• The current provided by the  $^{63}\text{Ni}$  source varies with the pressure

• This changes the reciprocation time of cantilever and RF-pulse

A typical pulse detected by the coil placed 0.1 m away from the DIP package, centered at 100 MHz

# IREMPG RF Transmitter

## Self-powered ARC Radios

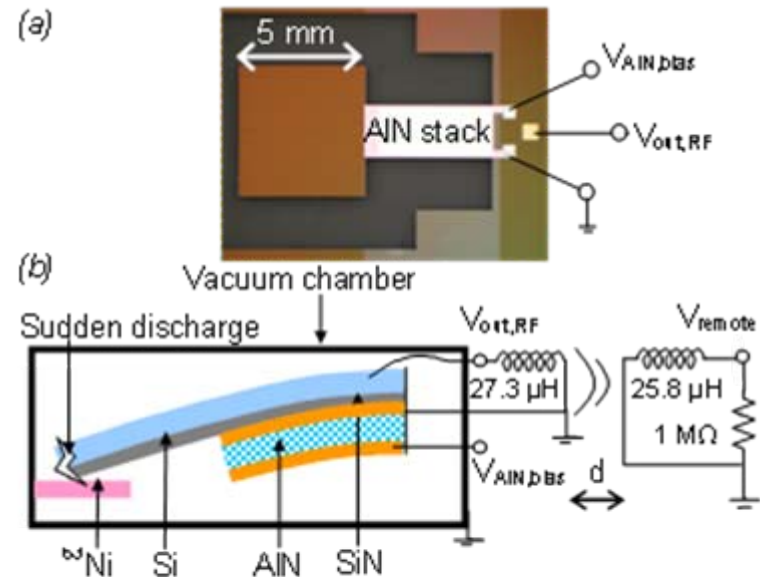
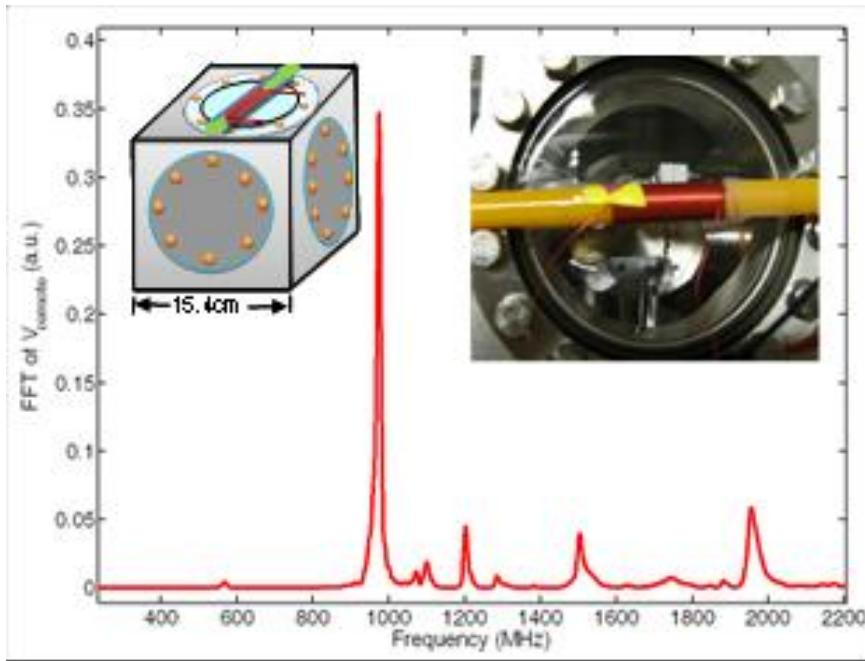
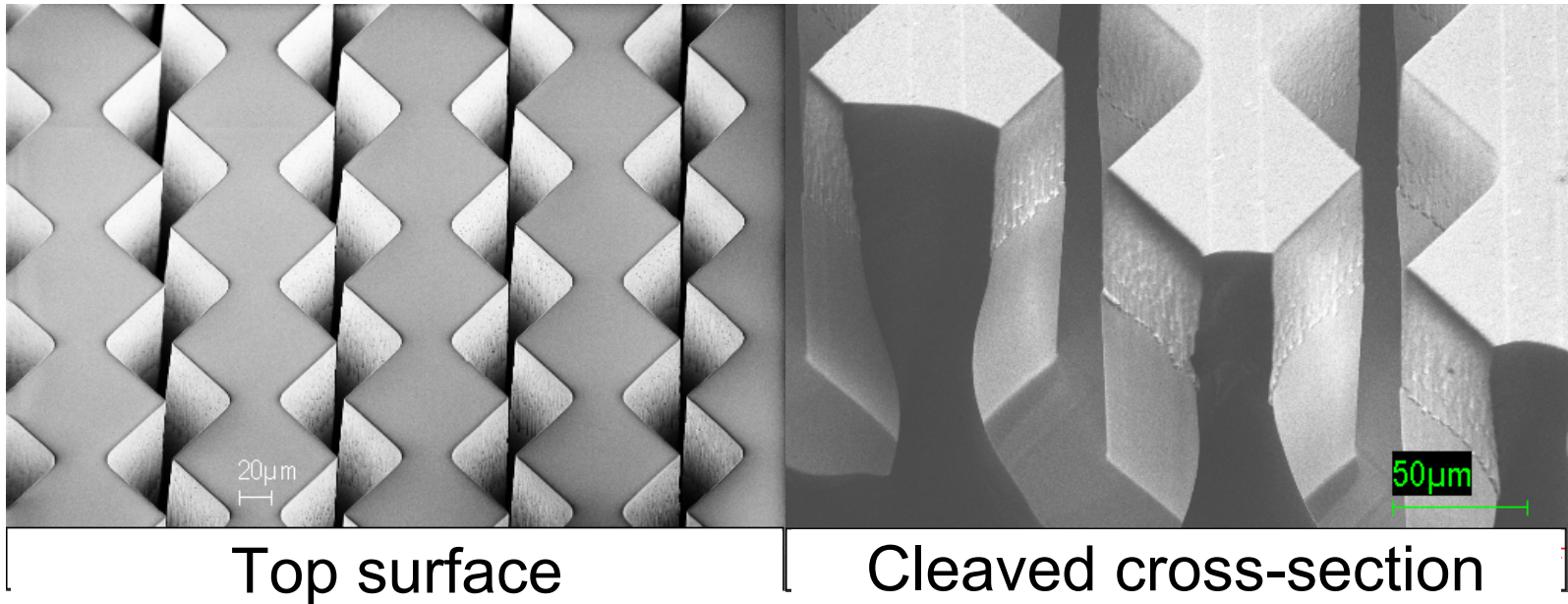


Figure 6. (a) Top-view photograph of the micro AIN-Si cantilever, and (b) schematic of wireless RF signal characterization set-up.

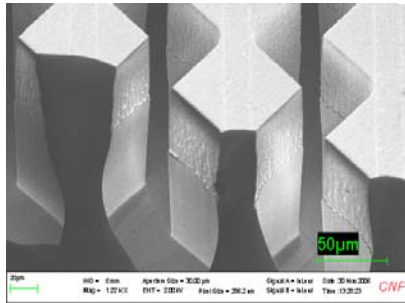
**High Energy  
Density  
Betavoltaics**

# SEMs of Microfabricated 3D Betavoltaic



# 3D Betavoltaics vs. Planar Betavoltaics for Same Substrate and Process Flow

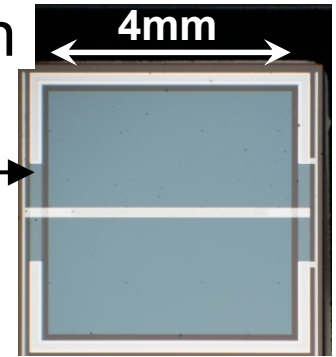
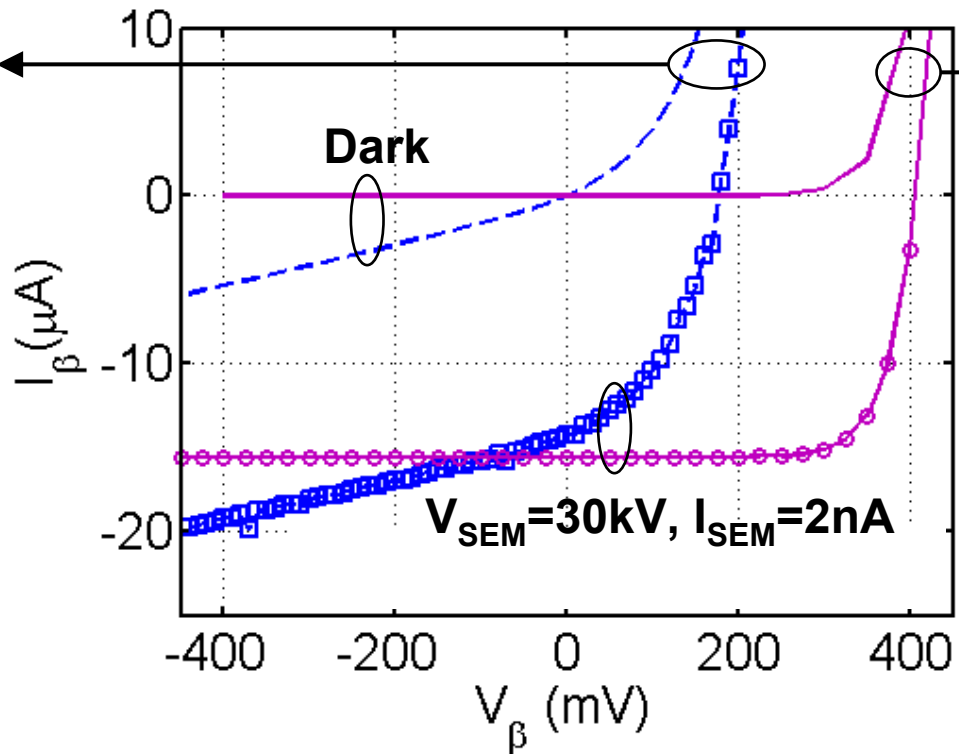
1 mm<sup>2</sup> SEM electron beam irradiation



0.64 cm<sup>2</sup> 3D betavoltaic chip

**High  $I_0$**

$V_{oc} = 180$  mV  
 FF = 43 %  
 $\eta_{\beta} = 1.61\%$



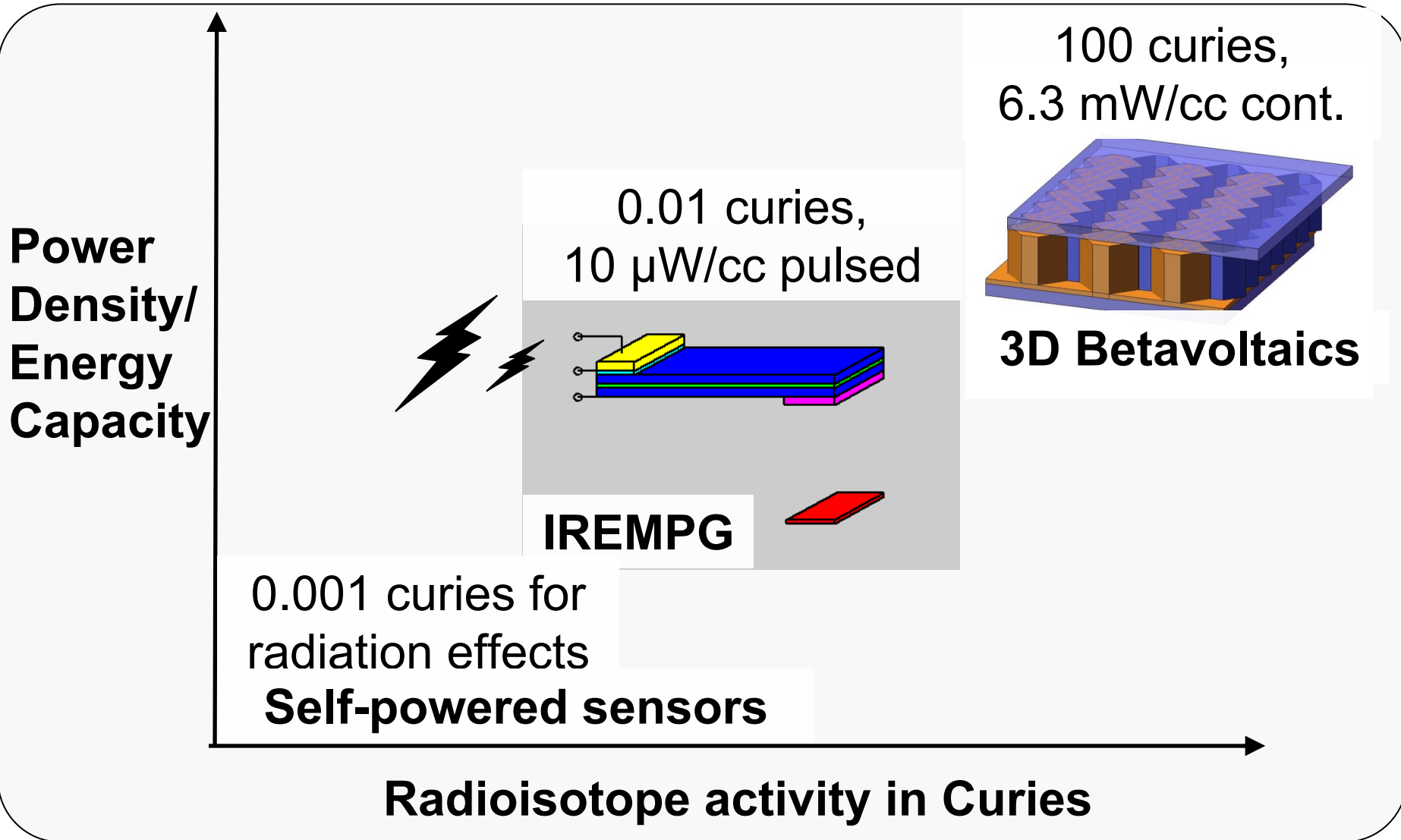
0.16 cm<sup>2</sup> planar betavoltaic chip

**Low  $I_0$**

$V_{oc} = 410$  mV  
 FF = 74 %  
 $\eta_{\beta} = 4.6\%$

**High Leakage leading to low efficiency**

# Radioisotopes in Microsystems



# Conclusions/Future

- **Radioisotopes (in particular pure beta emitters) can provide nano-thin film sources energy**
- **High energy particles require impedance matches – MEMS provides this in multiple ways: Pulsed RF, Pulsed Mechanical, DC**
- **Self-powered Light Sources, Vacuum Pumps, Cyclotrons, Counting clocks, random number generators – nuclear physics on a chip!**
- **NEXT: Packaged Self-Powered Sensor Node – operate at high and low temp, 100 year lifetime**